
4M x 32 bit DDR Synchronous DRAM (SDRAM)

Etron Confidential**Preliminary (Rev 1.2 Feb./2008)**

Features

- Fast clock rate: 200 MHz
- Differential Clock CK & \overline{CK} input
- 4 Bi-directional DQS. Data transactions on both edges of DQS (1DQS / Byte)
- DLL aligns DQ and DQS transitions
- Edge aligned data & DQS output
- Center aligned data & DQS input
- 4 internal banks, 1M x 32-bit for each bank
- Programmable mode and extended mode registers
 - CAS Latency: 3
 - Burst length: 2, 4, 8
 - Burst Type: Sequential & Interleave
- Full page burst length for sequential type only
- Start address of full page burst should be even
- All inputs except DQ's & DM are at the positive edge of the system clock
- No Write-Interrupted by Read function
- 4 individual DM control for write masking only
- Auto Refresh and Self Refresh
- 4096 refresh cycles / 64ms
- Power supplies :
 - VDD = 2.5V \pm 5%
 - VDDQ = 2.5V \pm 5%
- Interface : SSTL_2 I/O compatible
- Package: 144-ball TFBGA
 - Pb free

Overview

The EM6A9320 DDR SDRAM is a high-speed CMOS double data rate synchronous DRAM containing 128 Mbits. It is internally configured as a quad 1M x 32 DRAM with a synchronous interface (all signals are registered on the positive edge of the clock signal, CK).

Data outputs occur at both rising edges of CK and \overline{CK} . Read and write accesses to the SDRAM are burst oriented; accesses start at a selected location and continue for a programmed number of locations in a programmed sequence.

Accesses begin with the registration of a BankActivate command, which is then followed by a Read or Write command.

The EM6A9320 provides programmable Read or Write burst lengths of 2, 4, 8. An auto precharge function may be enabled to provide a self-timed row precharge that is initiated at the end of the burst sequence.

The refresh functions, either Auto or Self Refresh are easy to use.

In addition, EM6A9320 features programmable DLL option. By having a programmable mode register and extended mode register, the system can choose the most suitable modes to maximize its performance.

These devices are well suited for applications requiring high memory bandwidth, result in a device particularly well suited to high performance main memory and graphics applications.

Table1. Ordering Information

Part Number	Clock Frequency	Data Rate	Power Supply	Package
EM6A9320BI-5MG	200MHz	400Mbps/pin	VDD 2.5V, VDDQ 2.5V	TFBGA

BI: indicates TFBGA package

M : indicates in the last digit: indicates 0.11um process generation

G: indicates Pb Free for TFBGA Package

Etron Technology, Inc.

No. 6, Technology Rd. V, Science-Based Industrial Park, Hsinchu, Taiwan 30077, R.O.C.

TEL: (886)-3-5782345 FAX: (886)-3-5778671

Etron Technology, Inc., reserves the right to make changes to its products and specifications without notice.

Figure 1. Pin Assignment (FBGA 144Ball Top View)

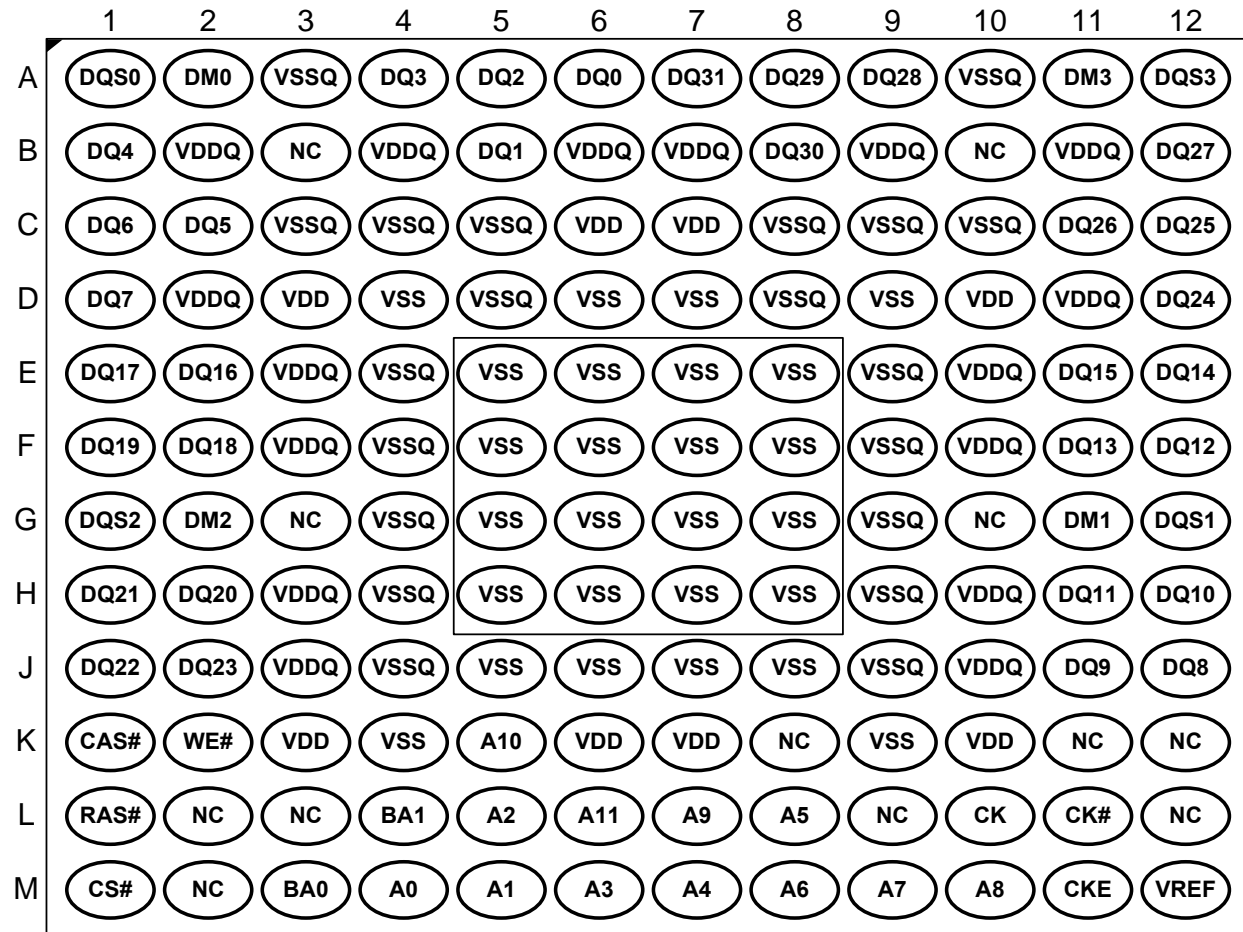
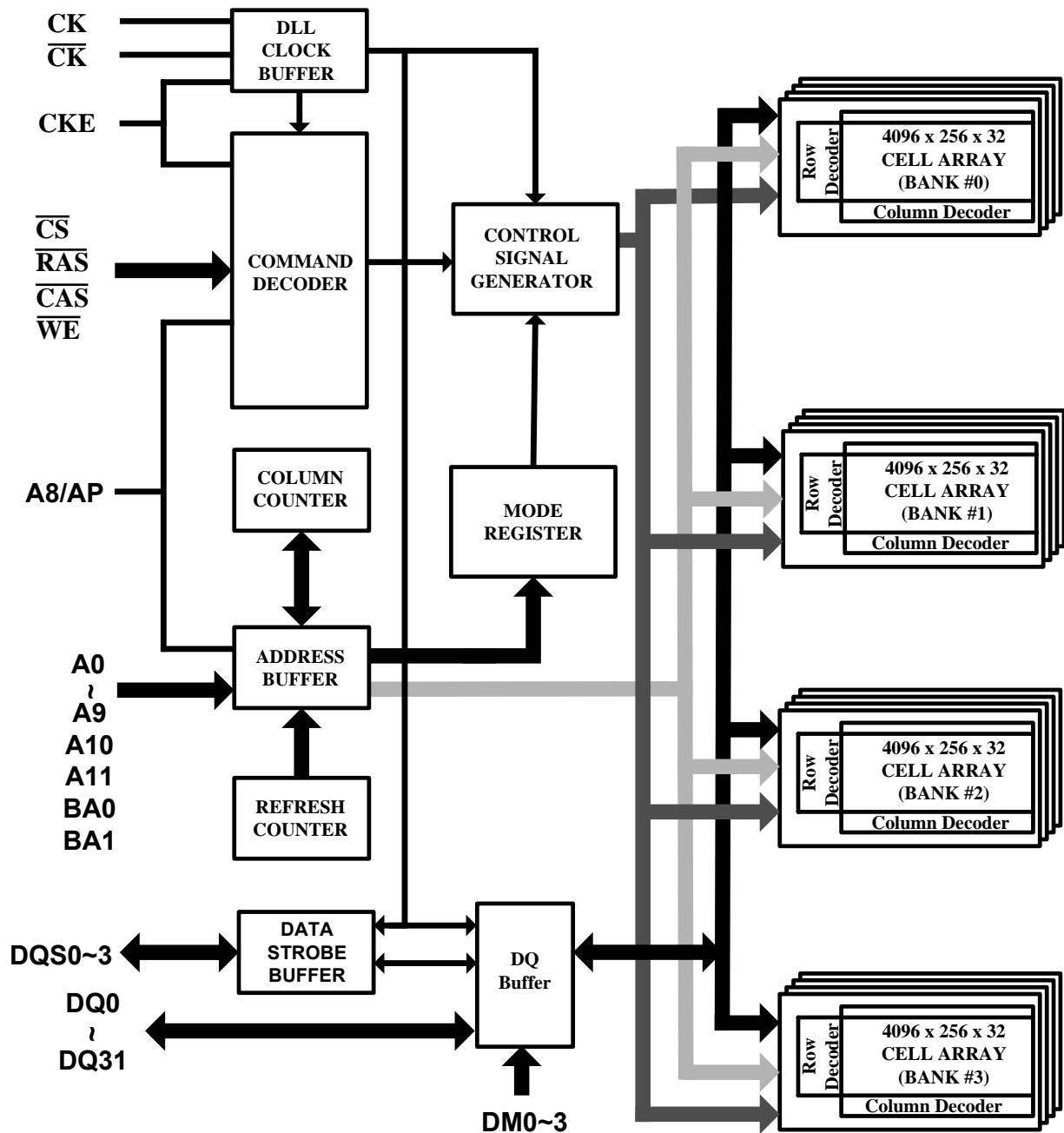


Table 2. Pin Assignment by Name (FBGA 144Ball)

Symbol	Location	Symbol	Location	Symbol	Location	Symbol	Location	Symbol	Location	Symbol	Location	Symbol	Location	Symbol	Location
A0	M4	DQ6	C1	DQ24	D12	CK	L10	VDDQ	B6	VSS	E5	VSS	J7	VSSQ	G4
A1	M5	DQ7	D1	DQ25	C12	\overline{CK}	L11	VDDQ	B7	VSS	E6	VSS	J8	VSSQ	G9
A2	L5	DQ8	J12	DQ26	C11	CKE	M11	VDDQ	B9	VSS	E7	VSS	K4	VSSQ	H4
A3	M6	DQ9	J11	DQ27	B12	\overline{CS}	M1	VDDQ	B11	VSS	E8	VSS	K9	VSSQ	H9
A4	M7	DQ10	H12	DQ28	A9	\overline{RAS}	L1	VDDQ	D2	VSS	F5	VSSQ	A3	VSSQ	J4
A5	L8	DQ11	H11	DQ29	A8	\overline{CAS}	K1	VDDQ	D11	VSS	F6	VSSQ	A10	VSSQ	J9
A6	M8	DQ12	F12	DQ30	B8	\overline{WE}	K2	VDDQ	E3	VSS	F7	VSSQ	C3	NC	B3
A7	M9	DQ13	F11	DQ31	A7	VREF	M12	VDDQ	E10	VSS	F8	VSSQ	C4	NC	B10
A8/AP	M10	DQ14	E12	DQS0	A1	VDD	C6	VDDQ	F3	VSS	G5	VSSQ	C5	NC	G3
A9	L7	DQ15	E11	DQS1	G12	VDD	C7	VDDQ	F10	VSS	G6	VSSQ	C8	NC	G10
A10	K5	DQ16	E2	DQS2	G1	VDD	D3	VDDQ	H3	VSS	G7	VSSQ	C9	NC	K8
A11	L6	DQ17	E1	DQS3	A12	VDD	D10	VDDQ	H10	VSS	G8	VSSQ	C10	NC	K11
DQ0	A6	DQ18	F2	DM0	A2	VDD	K3	VDDQ	J3	VSS	H5	VSSQ	D5	NC	K12
DQ1	B5	DQ19	F1	DM1	G11	VDD	K6	VDDQ	J10	VSS	H6	VSSQ	D8	NC	L2
DQ2	A5	DQ20	H2	DM2	G2	VDD	K7	VSS	D4	VSS	H7	VSSQ	E4	NC	L3
DQ3	A4	DQ21	H1	DM3	A11	VDD	K10	VSS	D6	VSS	H8	VSSQ	E9	NC	L9
DQ4	B1	DQ22	J1	BA0	M3	VDDQ	B2	VSS	D7	VSS	J5	VSSQ	F4	NC	L12
DQ5	C2	DQ23	J2	BA1	L4	VDDQ	B4	VSS	D9	VSS	J6	VSSQ	F9	NC	M2

Figure 2. Block Diagram



Pin Descriptions

Table 3. Pin Details of EM6A9320

Symbol	Type	Description
CK, \overline{CK}	Input	Differential Clock: CK, \overline{CK} are driven by the system clock. All SDRAM input commands are sampled on the positive edge of CK. Both CK and \overline{CK} increment the internal burst counter and controls the output registers.
CKE	Input	Clock Enable: CKE activates (HIGH) and deactivates (LOW) the CK signal. If CKE goes low synchronously with clock, the internal clock is suspended from the next clock cycle and the state of output and burst address is frozen as long as the CKE remains low. When all banks are in the idle state, deactivating the clock controls the entry to the Power Down and Self Refresh modes.
BA0, BA1	Input	Bank Activate: BA0 and BA1 defines to which bank the BankActivate, Read, Write, or BankPrecharge command is being applied. They also define which Mode Register or Extended Mode Register is loaded during a Mode Register Set command.
A0-A11	Input	Address Inputs: A0-A11 are sampled during the Bank Activate command (row address A0-A11) and Read/Write command (column address A0-A7 with A8 defining Auto Precharge) to select one location out of the 256K available in the respective bank. During a Precharge command, A8 is sampled to determine if all banks are to be precharged (A8 = HIGH). The address inputs also provide the op-code during a Mode Register Set or Extended Mode Register Set command.
\overline{CS}	Input	Chip Select: \overline{CS} enables (sampled LOW) and disables (sampled HIGH) the command decoder. All commands are masked when \overline{CS} is sampled HIGH. \overline{CS} provides for external bank selection on systems with multiple banks. It is considered part of the command code.
\overline{RAS}	Input	Row Address Strobe: The \overline{RAS} signal defines the operation commands in conjunction with the \overline{CAS} and \overline{WE} signals and is latched at the positive edges of CK. When \overline{RAS} and \overline{CS} are asserted "LOW" and \overline{CAS} is asserted "HIGH" either the BankActivate command or the Precharge command is selected by the \overline{WE} signal. When the \overline{WE} is asserted "HIGH," the BankActivate command is selected and the bank designated by BA is turned on to the active state. When the \overline{WE} is asserted "LOW," the Precharge command is selected and the bank designated by BA is switched to the idle state after the precharge operation.
\overline{CAS}	Input	Column Address Strobe: The \overline{CAS} signal defines the operation commands in conjunction with the \overline{RAS} and \overline{WE} signals and is latched at the positive edges of CK. When \overline{RAS} is held "HIGH" and \overline{CS} is asserted "LOW" the column access is started by asserting \overline{CAS} "LOW" Then, the Read or Write command is selected by asserting \overline{WE} "HIGH" or "LOW".
\overline{WE}	Input	Write Enable: The \overline{WE} signal defines the operation commands in conjunction with the \overline{RAS} and \overline{CAS} signals and is latched at the positive edges of CK. The \overline{WE} input is used to select the BankActivate or Precharge command and Read or Write command.
DQS0-DQS3	Input / Output	Bidirectional Data Strobe: The DQSx signals are mapped to the following data bytes: DQS0 to DQ0-DQ7, DQS1 to DQ8-DQ15, DQS2 to DQ16-DQ23, DQS3 to DQ24-DQ31.
DM0 - DM3	Input	Data Input Mask: DM0-DM3 are byte specific. Input data is masked when DM is sampled HIGH during a write cycle. DM3 masks DQ31-DQ24, DM2 masks DQ23-DQ16, DM1 masks DQ15-DQ8, and DM0 masks DQ7-DQ0.
DQ0 - DQ31	Input / Output	Data I/O: The DQ0-DQ31 input and output data are synchronized with the positive edges of CK and \overline{CK} . The I/Os are byte-maskable during Writes.
V _{DD}	Supply	Power Supply: Power for the input buffers and core logic.

V _{SS}	Supply	Ground: Ground for the input buffers and core logic.
V _{DDQ}	Supply	DQ Power: Provide isolated power to DQs for improved noise immunity.
V _{SSQ}	Supply	DQ Ground: Provide isolated ground to DQs for improved noise immunity.
V _{REF}	Supply	Reference Voltage for Inputs: +0.5 x V _{DDQ}
NC	-	No Connect: These pins should be left unconnected.

Note: The timing reference point for the differential clocking is the cross point of the CK and \overline{CK} . For any applications using the single ended clocking, apply V_{REF} to \overline{CK} pin.

Operation Mode

Fully synchronous operations are performed to latch the commands at the positive edges of CK . Table 2 shows the truth table for the operation commands.

Table 4. Truth Table (Note (1), (2))

Command	State	CKEn-1	CKEn	DM	BA1	BA0	A8	A11-A9, A7-0	\overline{CS}	\overline{RAS}	\overline{CAS}	\overline{WE}
BankActivate	Idle ⁽³⁾	H	X	X	V	V	Row Address		L	L	H	H
BankPrecharge	Any	H	X	X	V	V	L	X	L	L	H	L
PrechargeAll	Any	H	X	X	X	X	H	X	L	L	H	L
Write	Active ⁽³⁾	H	X	V	V	V	L	Column Address A0-A7	L	H	L	L
Write and AutoPrecharge	Active ⁽³⁾	H	X	V	V	V	H		L	H	L	L
Read	Active ⁽³⁾	H	X	X	V	V	L		L	H	L	H
Read and Autoprecharge	Active ⁽³⁾	H	X	X	V	V	H		L	H	L	H
Mode Register Set	Idle	H	X	X	L	L	OP code		L	L	L	L
Extended Mode Register Set	Idle	H	X	X	L	H			L	L	L	L
No-Operation	Any	H	X	X	X	X	X	X	L	H	H	H
Device Deselect	Any	H	X	X	X	X	X	X	H	X	X	X
Burst Stop	Active ⁽⁴⁾	H	X	X	X	X	X	X	L	H	H	L
AutoRefresh	Idle	H	H	X	X	X	X	X	L	L	L	H
SelfRefresh Entry	Idle	H	L	X	X	X	X	X	L	L	L	H
SelfRefresh Exit	Idle (Self Refresh)	L	H	X	X	X	X	X	H	X	X	X
									L	H	H	H
Power Down Mode Entry	Idle/Active ⁽⁵⁾	H	L	X	X	X	X	X	H	X	X	X
									L	H	H	H
Power Down Mode Exit	Any (Power Down)	L	H	X	X	X	X	X	H	X	X	X
									L	H	H	H
Data Write/Output Enable	Active	H	X	L	X	X	X	X	X	X	X	X
Data Mask/Output Disable	Active	H	X	H	X	X	X	X	X	X	X	X

- Note:**
1. V = Valid data, X = Don't Care, L = Low level, H = High level
 2. CKEn signal is input level when commands are provided.
CKEn-1 signal is input level one clock cycle before the commands are provided.
 3. These are states of bank designated by BA0, BA1 signals.
 4. Read burst stop with BST command for all burst types.
 5. Power Down Mode can not enter in the burst operation.
When this command is asserted in the burst cycle, device state is clock suspend mode.

Mode Register Set (MRS)

The mode register is divided into various fields depending on functionality.

- **Burst Length Field (A2~A0)**
This field specifies the data length of column access using the A2~A0 pins and selects the Burst Length to be 2, 4, 8.

Table 5. Burst Length

A2	A1	A0	Burst Length
0	0	0	Reserved
0	0	1	2
0	1	0	4
0	1	1	8
1	0	0	Reserved
1	0	1	Reserved
1	1	0	Reserved
1	1	1	Reserved

- **Addressing Mode Select Field (A3)**
The Addressing Mode can be one of two modes, both Interleave Mode or Sequential Mode. Both Sequential Mode and Interleave Mode support burst length of 2, 4, and 8.

Table 6. Addressing Mode

A3	Addressing Mode
0	Sequential
1	Interleave

--- Addressing Sequence of Sequential Mode

An internal column address is performed by increasing the address from the column address which is input to the device. The internal column address is varied by the Burst Length as shown in the following table.

Table 7. Sequential Addressing Mode

Data n	0	1	2	3	4	5	6	7
Column Address	n	n+1	n+2	n+3	n+4	n+5	n+6	n+7
	2 words							
Burst Length	4 words							
	8 words							

--- Addressing Sequence of Interleave Mode

A column access is started in the input column address and is performed by inverting the address bits in the sequence shown in the following table.

Table 8. Interleave Addressing Mode

Data n	Column Address								Burst Length	
Data 0	A7	A6	A5	A4	A3	A2	A1	A0	4 words	8 words
Data 1	A7	A6	A5	A4	A3	A2	A1	A0#		
Data 2	A7	A6	A5	A4	A3	A2	A1#	A0		
Data 3	A7	A6	A5	A4	A3	A2	A1#	A0#		
Data 4	A7	A6	A5	A4	A3	A2#	A1	A0		
Data 5	A7	A6	A5	A4	A3	A2#	A1	A0#		
Data 6	A7	A6	A5	A4	A3	A2#	A1#	A0		
Data 7	A7	A6	A5	A4	A3	A2#	A1#	A0#		

- CAS Latency Field (A6~A4)

This field specifies the number of clock cycles from the assertion of the Read command to the first read data. The minimum whole value of CAS Latency depends on the frequency of CK. The minimum whole value satisfying the following formula must be programmed into this field.

$$t_{CAC}(\min) \leq \text{CAS Latency} \times t_{CK}$$

Table 9. CAS Latency

A6	A5	A4	CAS Latency
0	0	0	Reserved
0	0	1	Reserved
0	1	0	Reserved
0	1	1	3 clocks
1	0	0	Reserved
1	0	1	Reserved
1	1	0	Reserved
1	1	1	Reserved

- Test Mode field (A8~A7)

These two bits are used to enter the test mode and must be programmed to "00" in normal operation.

Table 10. Test Mode

A8	A7	Test Mode
0	0	Normal mode
1	0	DLL Reset
X	1	Test mode

- (BA0, BA1)

Table 11. MRS/EMRS

BA1	BA0	An ~ A0
RFU	0	MRS Cycle
RFU	1	Extended Functions (EMRS)

Extended Mode Register Set (EMRS)

The Extended Mode Register Set stores the data for enabling or disabling DLL and selecting output driver strength. The default value of the extended mode register is not defined, therefore must be written after power up for proper operation. The extended mode register is written by asserting low on \overline{CK} , \overline{RAS} , \overline{CAS} , and \overline{WE} . The state of A0, A2 ~ A5, A7 ~ A11 and BA1 is written in the mode register in the same cycle as \overline{CK} , \overline{RAS} , \overline{CAS} , and \overline{WE} going low. The DDR SDRAM should be in all bank precharge with CKE already high prior to writing into the extended mode register. A1 and A6 are used for setting driver strength to normal, weak or matched impedance. Two clock cycles are required to complete the write operation in the extended mode register. The mode register contents can be changed using the same command and clock cycle requirements during operation as long as all banks are in the idle state. A0 is used for DLL enable or disable. "High" on BA0 is used for EMRS. Refer to the table for specific codes.

Table 12. Extended Mode Register Bitmap

BA1	BA0	A11	A10	A9	A8	A7	A6	A5	A4	A3	A2	A1	A0	
0	1	RFU must be set to "0"					DS1	RFU must be set to "0"					DS0	DLL

BA0	Mode	A6	A1	Drive Strength	Strength	Comment	A0	DLL
0	MRS	0	0	Full	100%		0	Enable
1	EMRS	0	1	SSTL-2 weak	60%		1	Disable
		1	0	RFU	RFU	Do not use		
		1	1	Matched impedance	30%	Output driver matches impedance		

Table 13. AC Timing Table

Parameter	Min	Max
t_{WRIDON}	0ns	30ns
$t_{WRIDOFF}$	0ns	30ns

Table 14. Absolute Maximum Rating

Symbol	Item	Rating	Unit	Note
		-5		
V _{IN} , V _{OUT}	Input, Output Voltage	- 0.3 ~ V _{DDQ} +0.3	V	1
V _{DD} , V _{DDQ}	Power Supply Voltage	-0.3 ~ 3.6	V	1
T _A	Operating Temperature	0~70	°C	1
T _{STG}	Storage Temperature	- 55~150	°C	1
T _{SOLDER}	Soldering Temperature (10s)	260	°C	1
P _D	Power Dissipation	2.0	W	1
I _{OUT}	Short Circuit Output Current	50	mA	1

Note1: Stress greater than those listed under “Absolute Maximum Ratings” may cause permanent damage of the devices

Table 15. Recommended D.C. Operating Conditions (SSTL_2 In/Out, T_A = 0 ~ 70 °C)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Note
V _{DD}	Power Supply Voltage	2.375	2.5	2.625	V	1
V _{DDQ}	Power Supply Voltage(for I/O)	2.375	2.5	2.625	V	1
V _{REF}	Input Reference Voltage	0.49 x V _{DDQ}	-	0.51 x V _{DDQ}	V	
V _{TT}	Termination Voltage	V _{REF} - 0.04	V _{REF}	V _{REF} + 0.04	V	
V _{IH(DC)}	Input High Voltage	V _{REF} + 0.15	-	V _{DDQ} + 0.3	V	
V _{IL(DC)}	Input Low Voltage	V _{SSQ} - 0.3	-	V _{REF} - 0.15	V	
V _{OH}	Output High Voltage	V _{tt} + 0.76	-	-	V	I _{OH} = -15.2 mA
V _{OL}	Output Low Voltage	-	-	V _{tt} - 0.76	V	I _{OL} = +15.2 mA
I _{IL}	Input Leakage Current	- 5	-	5	μA	
I _{OL}	Output Leakage Current	- 5	-	5	μA	

Note : 1. Under all conditions V_{DDQ} must be less than or equal to V_{DD}.

Table 16. Capacitance (V_{DD} = 2.5V± 5%, f = 1MHz, T_a = 25 °C)

Symbol	Parameter	Min.	Max.	Unit
C _{IN1}	Input Capacitance (A0~A11, BA0, BA1)	4	5	pF
C _{IN2}	Input Capacitance (CK, /CK, CKE, /CS, /RAS, /CAS, /WE)	3	5	pF
C _{I/O}	DQ, DQS Input/Output Capacitance	6	8	pF
C _{IN3}	DM, Input Capacitance	6	8	pF

Note: These parameters are guaranteed by design, periodically sampled and are not 100% tested.

Table 17. Decoupling Capacitance Guide Line

Symbol	Parameter	Value	Unit
C _{DC1}	Decoupling Capacitance between V _{DD} and V _{SS}	0.1+0.01	uF
C _{DC2}	Decoupling Capacitance between V _{DDQ} and V _{SSQ}	0.1+0.01	uF

Table 18. Recommended D.C. Operating Conditions (VDD=2.5V ± 5%, Ta=0~70°C)

Parameter & Test Condition	Symbol	-5	Unit	Note
		MAX		
OPERATING CURRENT : One bank; Active-Precharge; tRC=tRC(min); tCK=tCK(min); DQ,DM and DQS inputs changing once per clock cycle; Address and control inputs changing once every two clock cycles.	IDD0	210	mA	
OPERATING CURRENT : One bank; Active-Read-Precharge; BL=4; CL=4; tRCRD=4*tCK; tRC=tRC(min); tCK=tCK(min); Iout=0mA; Address and control inputs changing once per clock cycle	IDD1	240	mA	
PRECHARGE POWER-DOWN STANDBY CURRENT : All banks idle; power-down mode; tCK=tCK(min); CKE=LOW	IDD2P	75	mA	
IDLE STANDBY CURRENT : CKE = HIGH; \overline{CS} =HIGH(DESELECT); All banks idle; tCK=tCK(min); Address and control inputs changing once per clock cycle; VIN=VREF for DQ, DQS and DM	IDD2N	100	mA	
ACTIVE POWER-DOWN STANDBY CURRENT : one bank active; power-down mode; CKE=LOW; tCK=tCK(min)	IDD3P	75	mA	
ACTIVE STANDBY CURRENT : \overline{CS} =HIGH;CKE=HIGH; one bank active ; tRC=tRC(max);tCK=tCK(min);Address and control inputs changing once per clock cycle; DQ,DQS,and DM inputs changing twice per clock cycle	IDD3N	220	mA	
OPERATING CURRENT BURST READ : BL=2; READS; Continuous burst; one bank active; Address and control inputs changing once per clock cycle; tCK=tCK(min); Iout=0mA;50% of data changing on every transfer	IDD4R	420	mA	
OPERATING CURRENT BURST Write : BL=2; WRITES; Continuous Burst ;one bank active; address and control inputs changing once per clock cycle; tCK=tCK(min); DQ,DQS,and DM changing twice per clock cycle; 50% of data changing on every transfer	IDD4W	420	mA	
AUTO REFRESH CURRENT : tRC=tRFC(min); tCK=tCK(min)	IDD5	300	mA	
SELF REFRESH CURRENT : Self Refresh Mode ; CKE<=0.2V;tCK=tCK(min)	IDD6	6	mA	
BURST OPERATING CURRENT 4 bank operation : Four bank interleaving READs; BL=4;with Auto Precharge; tRC=tRC(min); tCK=tCK(min); Address and control inputs change only during Active, READ , or WRITE command	IDD7	570	mA	

Note:

1. Stress greater than those listed under "Absolute Maximum Ratings" may cause permanent damage of the device.
2. All voltages are referenced to Vss.
3. These parameters depend on the cycle rate and these values are measured by the cycle rate under the minimum value of tCK and tRC. Input signals are changed one time during tCK.
4. Power-up sequence is described in previous page.

Table 19. Electrical Characteristics and Recommended A.C. Operating Conditions

(VDD = 2.5V ± 5%, Ta = 0–70 °C)

Symbol	Parameter	-5		Unit	
		Min	Max		
tCK	Clock cycle time	CL = 3	5	10	ns
tCH	Clock high level width		0.45	0.55	tCK
tCL	Clock low level width		0.45	0.55	tCK
tDQSCK	DQS-out access time from CK, \overline{CK}		0	1.4	ns
tAC	Output access time from CK, \overline{CK}		0	1.4	ns
tDQSQ	DQS-DQ Skew		-	0.4	ns
tRPRE	Read preamble		0.9	1.1	tCK
tRPST	Read postamble		0.4	0.6	tCK
tDQSS	CK to valid DQS-in		0.8	1.2	tCK
tWPRES	DQS-in setup time		0	-	tCK
tWPREH	DQS-in hold time		0.25	-	tCK
tWPST	DQS write postamble		0.4	0.6	tCK
tDQSH	DQS in high level pulse width		0.4	0.6	tCK
tDQSL	DQS in low level pulse width		0.4	0.6	tCK
tIS	Address and Control input setup time		1.0	-	ns
tIH	Address and Control input hold time		1.0	-	ns
tDS	DQ & DM setup time to DQS		0.5	-	ns
tDH	DQ & DM hold time to DQS		0.5	-	ns
tHP	Clock half period	tCLMIN or tCHMIN	-	-	ns
tQHS	Data hold skew factor		-	0.5	ns
tQH	Output DQS valid window	tHP - tQHS	-	-	ns
tRC	Row cycle time		12	-	tCK
tRFC	Refresh row cycle time		14	-	tCK
tRAS	Row active time		8	100K	tCK
tRCDRD	\overline{RAS} to \overline{CAS} Delay in Read		4	-	tCK
tRCDWR	RAS to CAS Delay in Write		2	-	tCK
tRP	Row precharge time		4	-	tCK
tRRD	Row active to Row active delay		2	-	tCK
tWR	Write recovery time		3	-	tCK
tCDLR	Last data in to Read command		2	-	tCK
tCCD	Col. Address to Col. Address delay		1	-	tCK
tMRD	Mode register set cycle time		2	-	tCK
tDAL	Auto precharge write recovery + Precharge		7	-	tCK
tXSA	Self refresh exit to read command delay		200	-	tCK
tPDEX	Power down exit time	tIS + 2tCK	-	-	ns
tREF	Refresh interval time		-	7.8	μs
tJ	Short term jitter		-	105	ps
tR, tF	CLK Rise time, Fall time		-	700	ps

Table 20. Recommended A.C. Operating Conditions ($T_a = 0\sim 70\text{ }^\circ\text{C}$, $V_{DD}=2.5 \pm 5\%$)

Parameter	Symbol	Min.	Max.	Unit	Note
Input High Voltage (AC)	$V_{IH} (AC)$	$V_{REF} + 0.4$		V	
Input Low Voltage (AC)	$V_{IL} (AC)$		$V_{REF} - 0.4$	V	
Input Different Voltage, CLK and \overline{CLK} inputs	$V_{ID} (AC)$	0.8	$V_{DDQ} + 0.6$	V	
Input Crossing Point Voltage, CLK and \overline{CLK} inputs	$V_{IX} (AC)$	$0.5 \cdot V_{DDQ} - 0.2$	$0.5 \cdot V_{DDQ} + 0.2$	V	

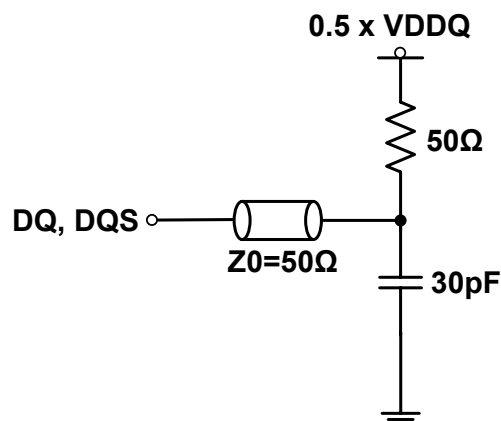
Note:

1. All voltages are referenced to V_{SS} .
2. These parameters depend on the cycle rate and these values are measured by the cycle rate under the minimum value of t_{CK} and t_{RC} . Input signals are changed one time during t_{CK} .
3. Power-up sequence is described in Note 5.
4. A.C. Test Conditions

Table 21. SSTL_2 Interface

Reference Level of Output Signals (V_{RFE})	$0.5 \cdot V_{DDQ}$
Output Load	Reference to the Test Load
Input Signal Levels	$V_{REF} + 0.4\text{ V} / V_{REF} - 0.4\text{ V}$
Input Signals Slew Rate	1 V/ns
Reference Level of Input Signals	$0.5 \cdot V_{DDQ}$

Figure 3. SSTL_2 A.C. Test Load



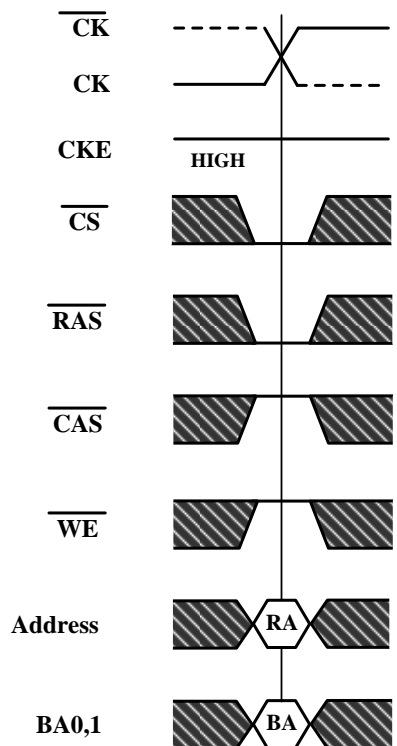
5. Power up Sequence

Power up must be performed in the following sequence.

- 1) Apply power to V_{DD} before or at the same time as V_{DDQ} , V_{TT} and V_{REF} when all input signals are held "NOP" state and maintain CKE "LOW".
- 2) Start clock and maintain stable condition for minimum 200us.
- 3) Issue a "NOP" command and keep CKE "HIGH"
- 4) Issue a "Precharge All" command.
- 5) Issue EMRS – enable DLL.
- 6) Issue MRS – reset DLL. (An additional 200 clock cycles are required to lock the DLL).
- 7) Precharge all banks of the device.
- 8) Issue two or more Auto Refresh commands.
- 9) Issue MRS – with A8 to low to initialize the mode register.

Timing Waveforms

Figure 4. Activating a Specific Row in a Specific Bank



RA=Row Address

BA=Bank Address

 Don't Care

Figure 5. t_{RCD} and t_{RRD} Definition

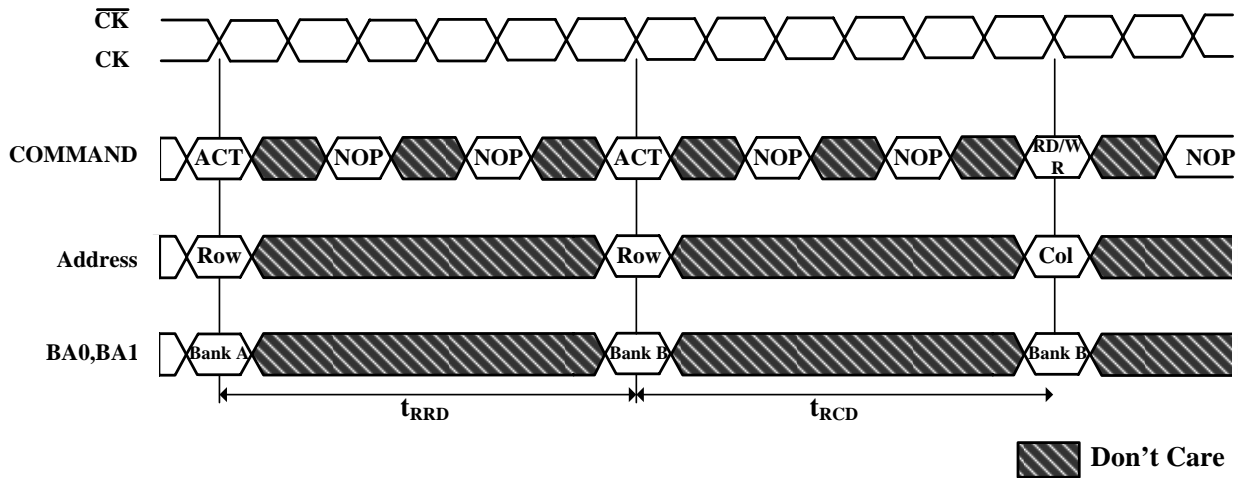


Figure 6. READ Command

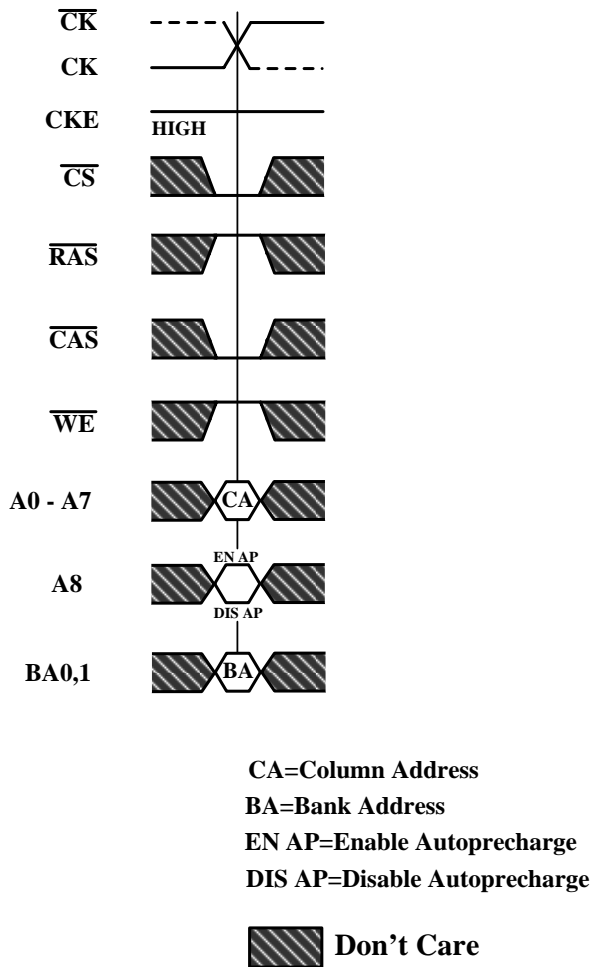
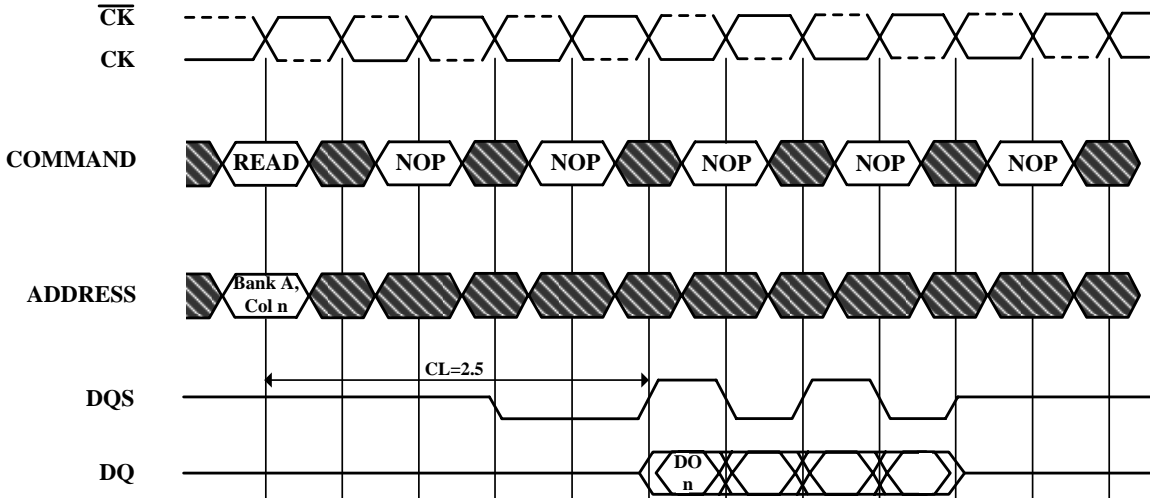


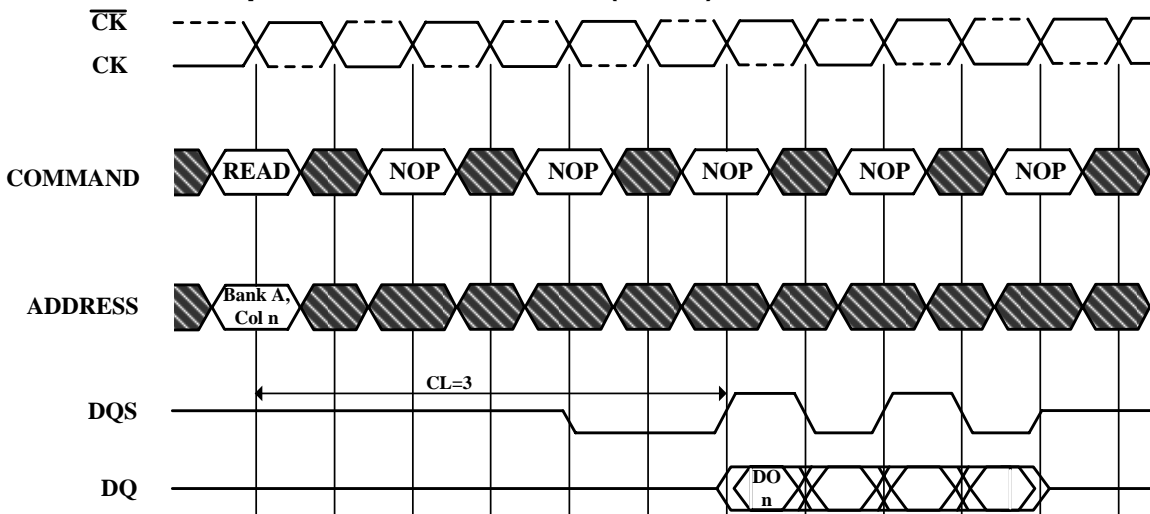
Figure 7. Read Burst Required CAS Latencies (CL=2.5)



DO n=Data Out from column n
 Burst Length=4
 3 subsequent elements of Data Out appear in the programmed order following DO n

 Don't Care

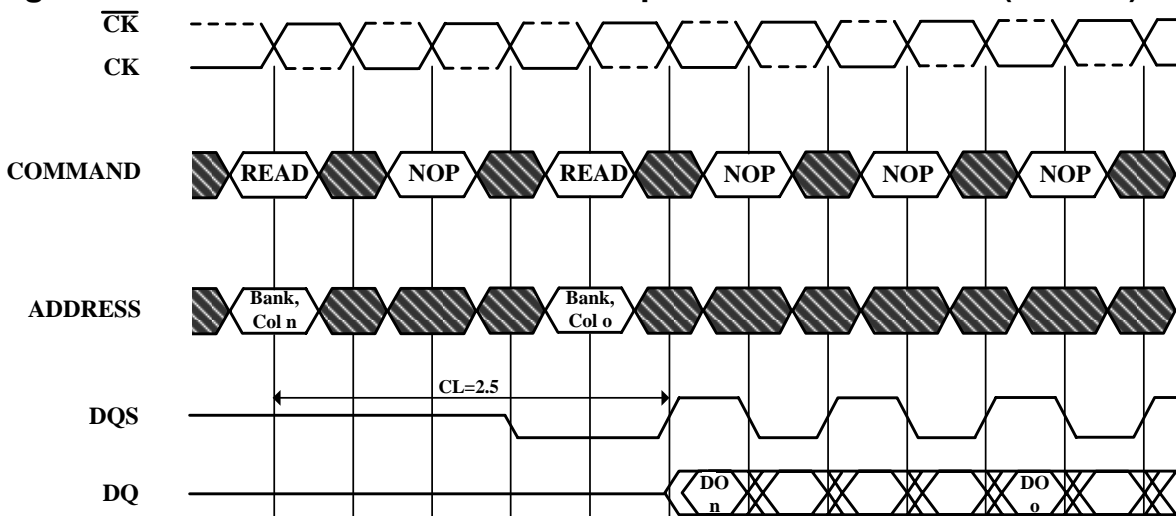
Read Burst Required CAS Latencies (CL=3)



DO n=Data Out from column n
 Burst Length=4
 3 subsequent elements of Data Out appear in the programmed order following DO n

 Don't Care

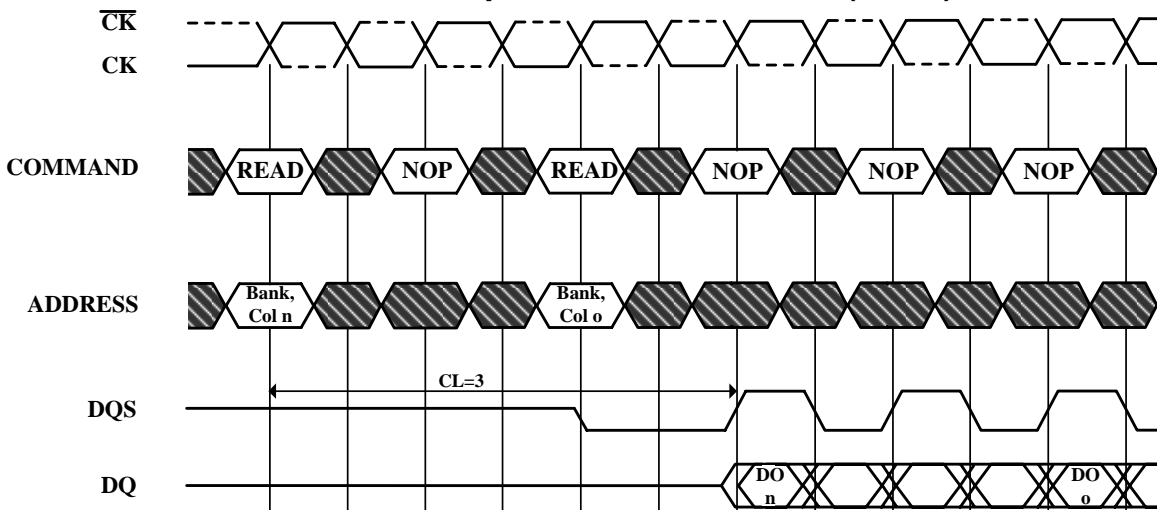
Figure 8. Consecutive Read Bursts Required CAS Latencies (CL=2.5)



DO n (or o)=Data Out from column n (or column o)
Burst Length=4 or 8 (if 4, the bursts are concatenated; if 8, the second burst interrupts the first)
3 subsequent elements of Data Out appear in the programmed order following DO n
3 (or 7) subsequent elements of Data Out appear in the programmed order following DO o
Read commands shown must be to the same device

 Don't Care

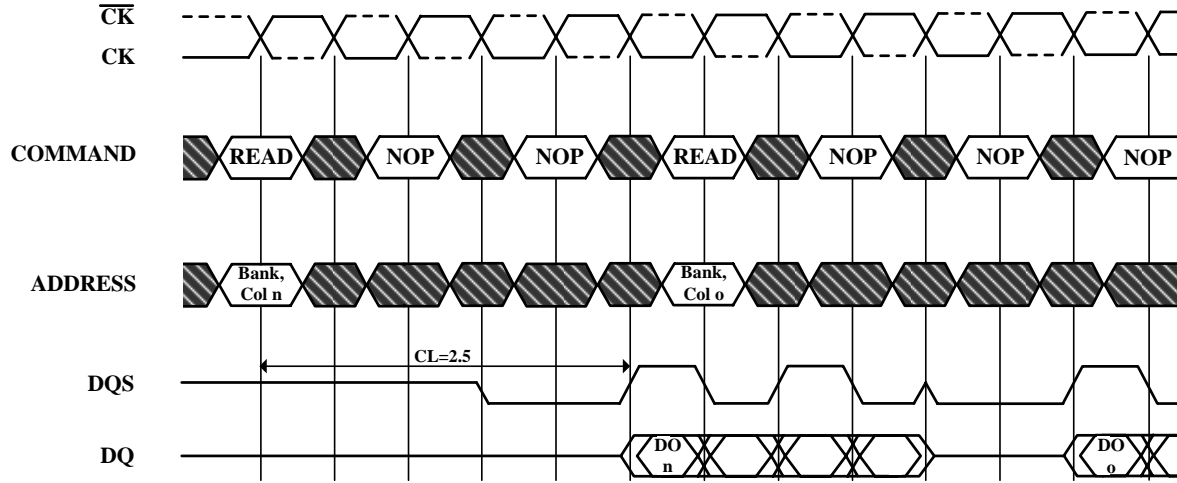
Consecutive Read Bursts Required CAS Latencies (CL=3)



DO n (or o)=Data Out from column n (or column o)
Burst Length=4 or 8 (if 4, the bursts are concatenated; if 8, the second burst interrupts the first)
3 subsequent elements of Data Out appear in the programmed order following DO n
3 (or 7) subsequent elements of Data Out appear in the programmed order following DO o
Read commands shown must be to the same device

 Don't Care

Figure 9. Non-Consecutive Read Bursts Required CAS Latencies (CL=2.5)



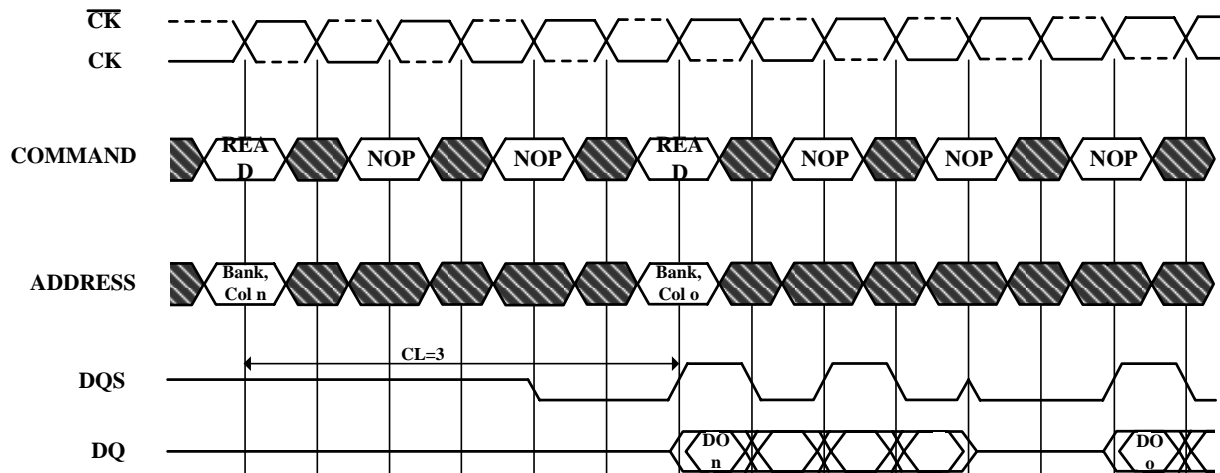
DO n (or o)=Data Out from column n (or column o)

Burst Length=4

3 subsequent elements of Data Out appear in the programmed order following DO n (and following DO o)

 Don't Care

Non-Consecutive Read Bursts Required CAS Latencies (CL=3)



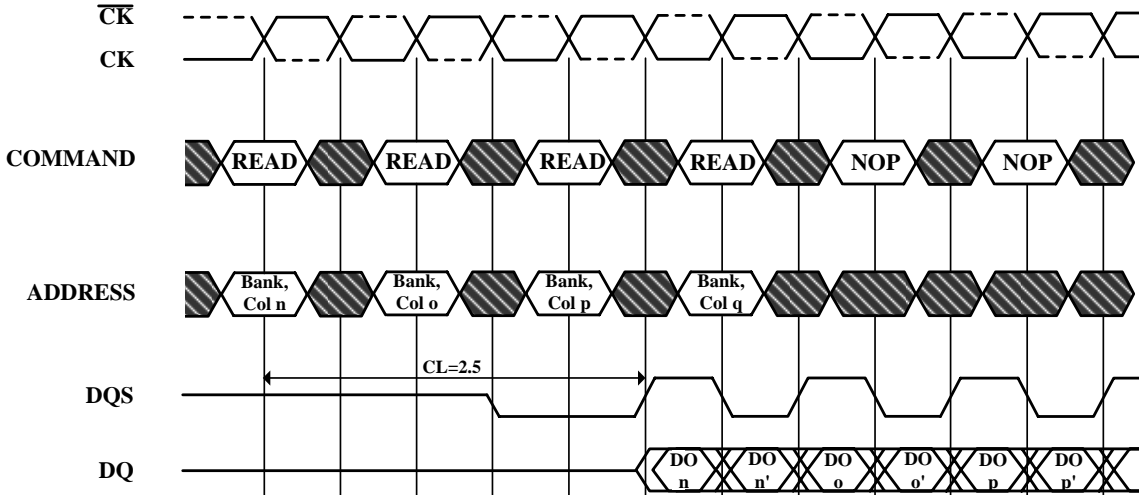
DO n (or o)=Data Out from column n (or column o)

Burst Length=4

3 subsequent elements of Data Out appear in the programmed order following DO n (and following DO o)

 Don't Care

Figure 10. Random Read Accesses Required CAS Latencies (CL=2.5)



DO n, etc. =Data Out from column n, etc.

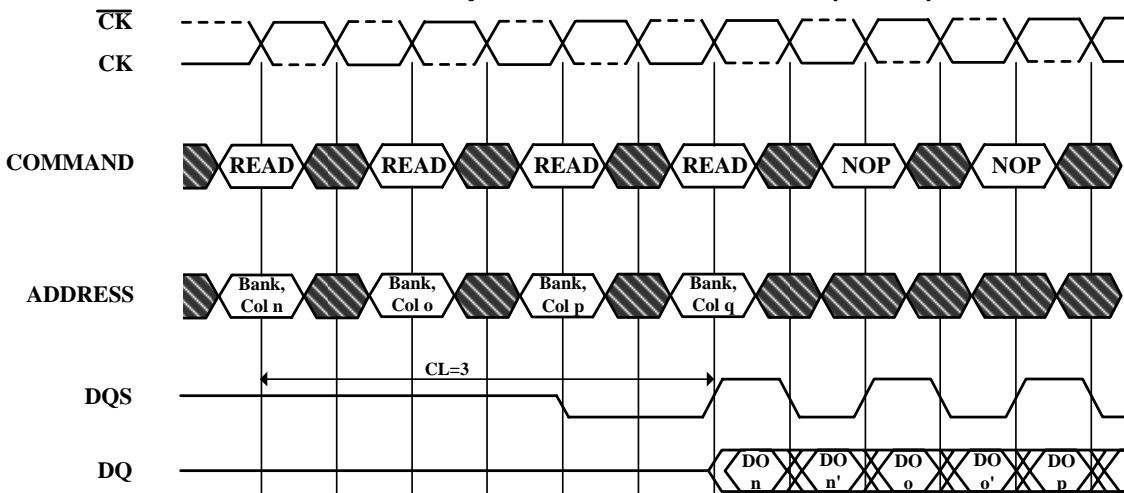
n', etc. =the next Data Out following DO n, etc. according to the programmed burst order

Burst Length=2,4 or 8 in cases shown. If burst of 4 or 8, the burst is interrupted

Reads are to active rows in any banks

 Don't Care

Random Read Accesses Required CAS Latencies (CL=3)



DO n, etc. =Data Out from column n, etc.

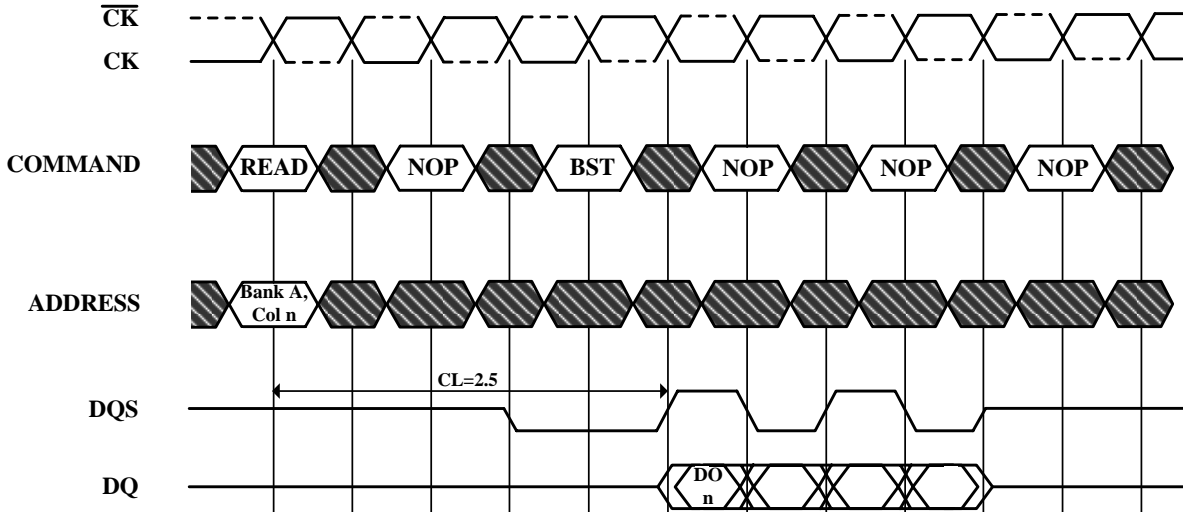
n', etc. =the next Data Out following DO n, etc. according to the programmed burst order

Burst Length=2,4 or 8 in cases shown. If burst of 4 or 8, the burst is interrupted

Reads are to active rows in any banks

 Don't Care

Figure 11. Terminating a Read Burst Required CAS Latencies (CL=2.5)



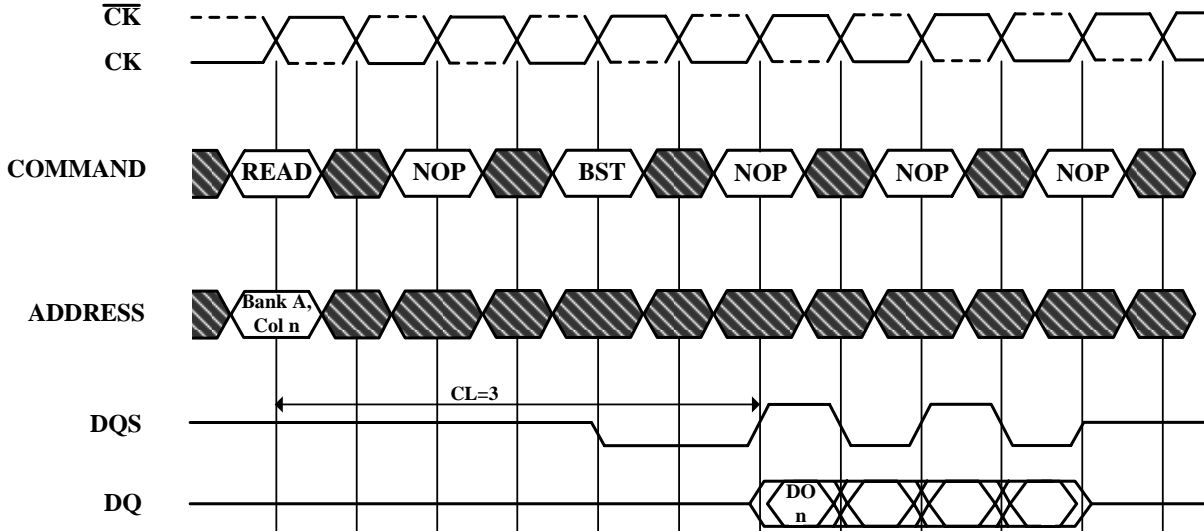
DO n = Data Out from column n

Cases shown are bursts of 8 terminated after 4 data elements

3 subsequent elements of Data Out appear in the programmed order following DO n

 Don't Care

Terminating a Read Burst Required CAS Latencies (CL=3)



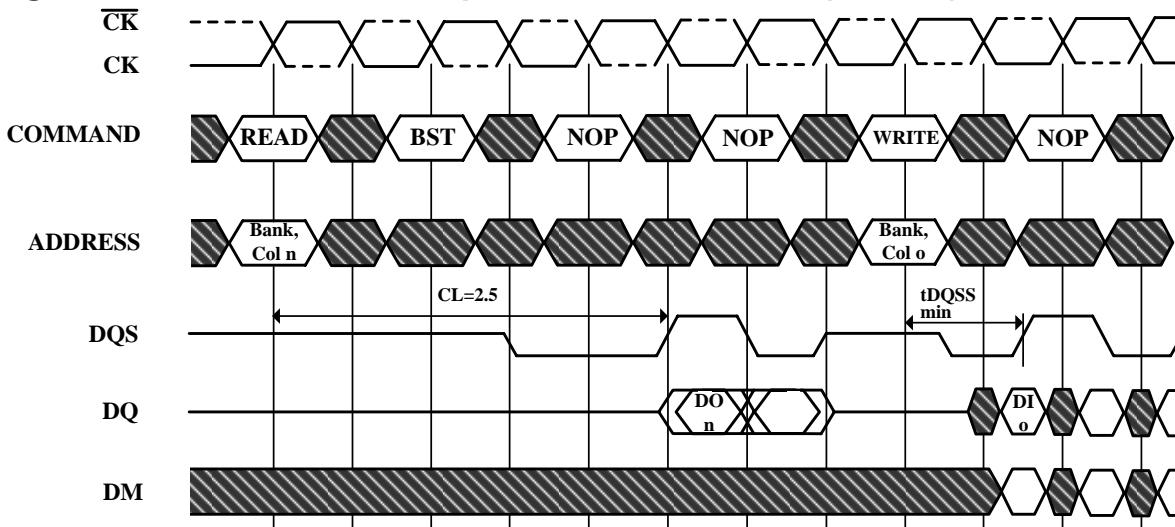
DO n = Data Out from column n

Cases shown are bursts of 8 terminated after 4 data elements

3 subsequent elements of Data Out appear in the programmed order following DO n

 Don't Care

Figure 12. Read to Write Required CAS Latencies (CL=2.5)



DO n (or o)= Data Out from column n (or column o)

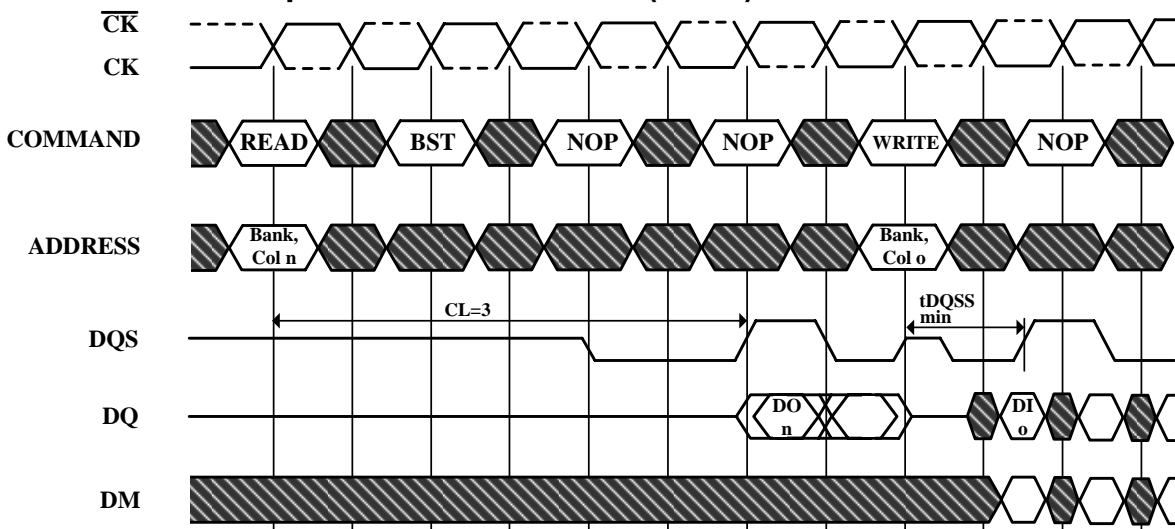
Burst Length= 4 in the cases shown (applies for bursts of 8 as well; if burst length is 2, the BST command shown can be NOP)

1 subsequent element of Data Out appears in the programmed order following DO n

Data in elements are applied following DI o in the programmed order

 Don't Care

Read to Write Required CAS Latencies (CL=3)



DO n (or o)= Data Out from column n (or column o)

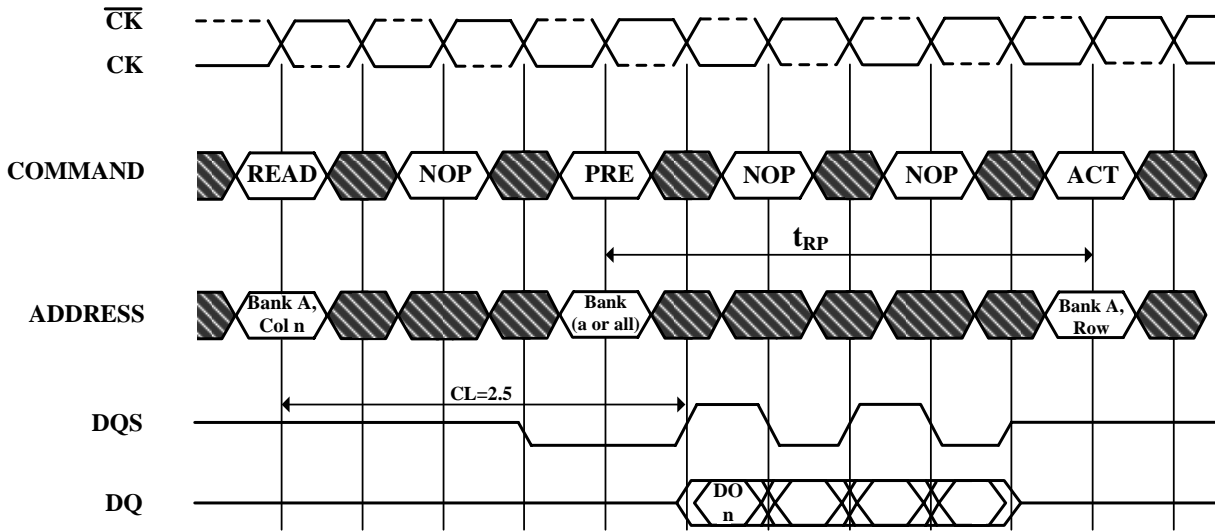
Burst Length= 4 in the cases shown (applies for bursts of 8 as well; if burst length is 2, the BST command shown can be NOP)

1 subsequent element of Data Out appears in the programmed order following DO n

Data in elements are applied following DI o in the programmed order

 Don't Care

Figure 13. Read to Precharge Required CAS Latencies (CL=2.5)



DO n = Data Out from column n

Cases shown are either uninterrupted bursts of 4, or interrupted bursts of 8
 3 subsequent elements of Data Out appear in the programmed order
 following DO n

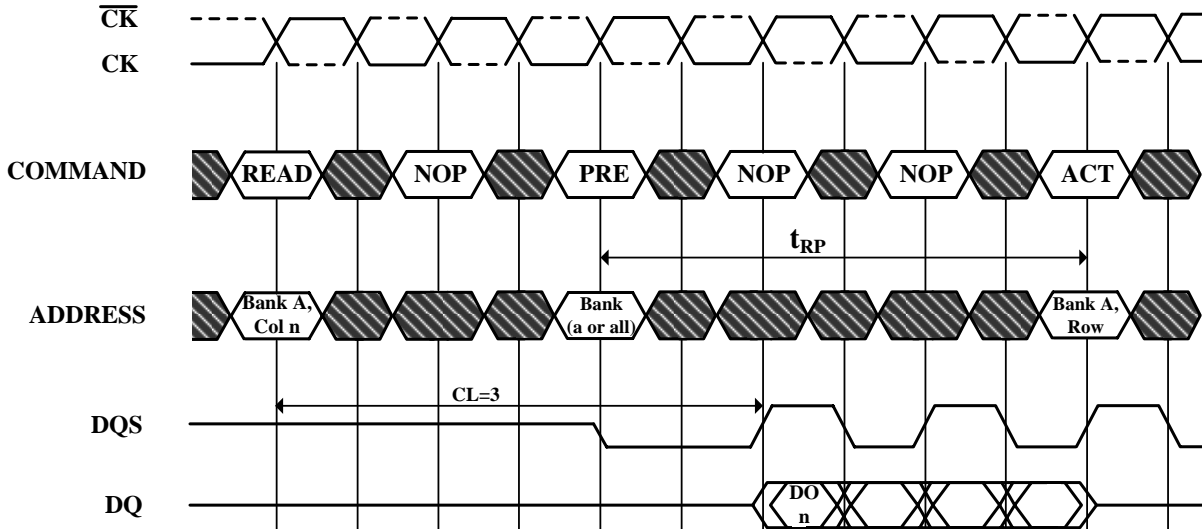
Precharge may be applied at $(BL/2) t_{CK}$ after the READ command

Note that Precharge may not be issued before t_{RAS} ns after the ACTIVE
 command for applicable banks

The Active command may be applied if t_{RC} has been met

 Don't Care

Read to Precharge Required CAS Latencies (CL=3)



DO n = Data Out from column n

Cases shown are either uninterrupted bursts of 4, or interrupted bursts of 8
3 subsequent elements of Data Out appear in the programmed order
following DO n

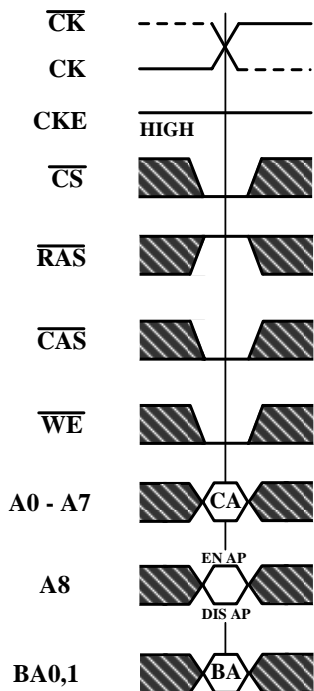
Precharge may be applied at $(BL/2) t_{CK}$ after the READ command

Note that Precharge may not be issued before t_{RAS} ns after the ACTIVE
command for applicable banks

The Active command may be applied if t_{RC} has been met

 Don't Care

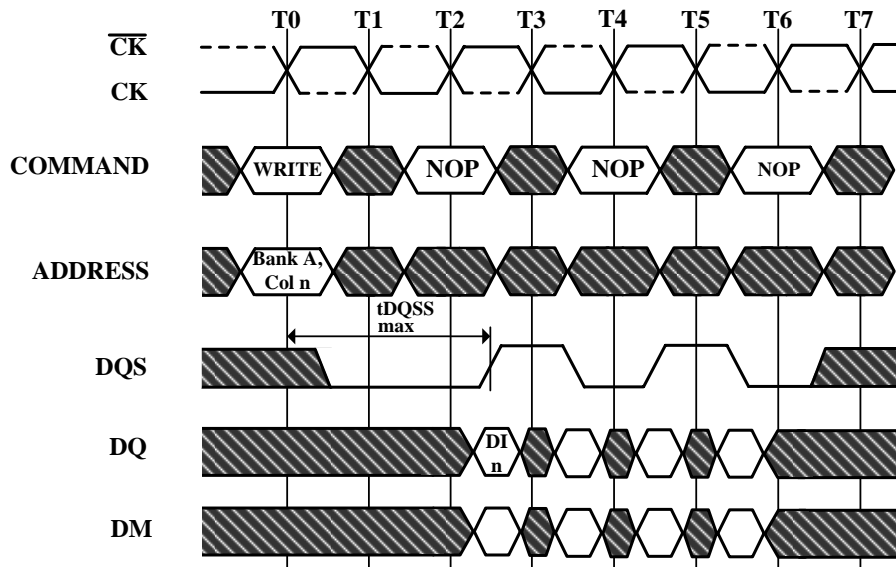
Figure 14. Write Command



CA=Column Address
 BA=Bank Address
 EN AP=Enable Autoprecharge
 DIS AP=Disable Autoprecharge

 Don't Care

Figure 15. Write Max DQSS



DI_n = Data In for column n

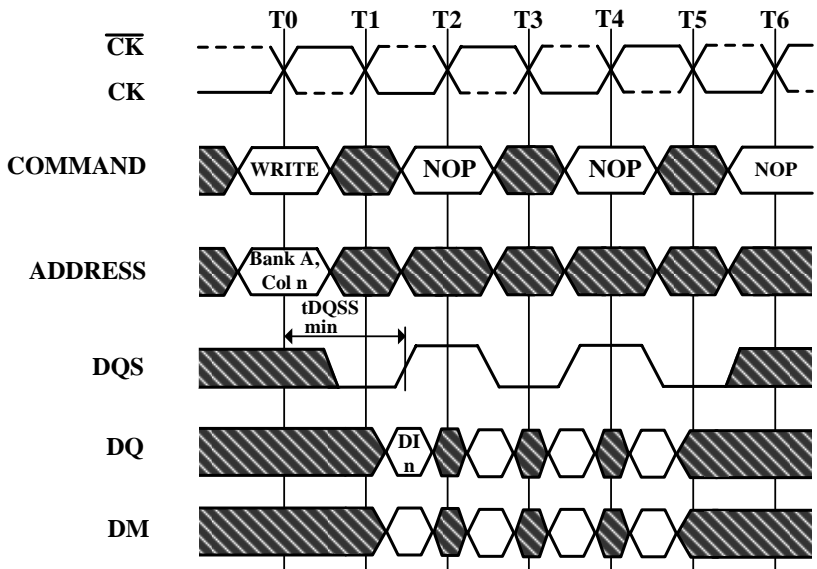
3 subsequent elements of Data In are applied in the programmed order following DI_n

A non-interrupted burst of 4 is shown

A8 is LOW with the WRITE command (AUTO PRECHARGE disabled)

 Don't Care

Figure 16. Write Min DQSS



DI n = Data In for column n

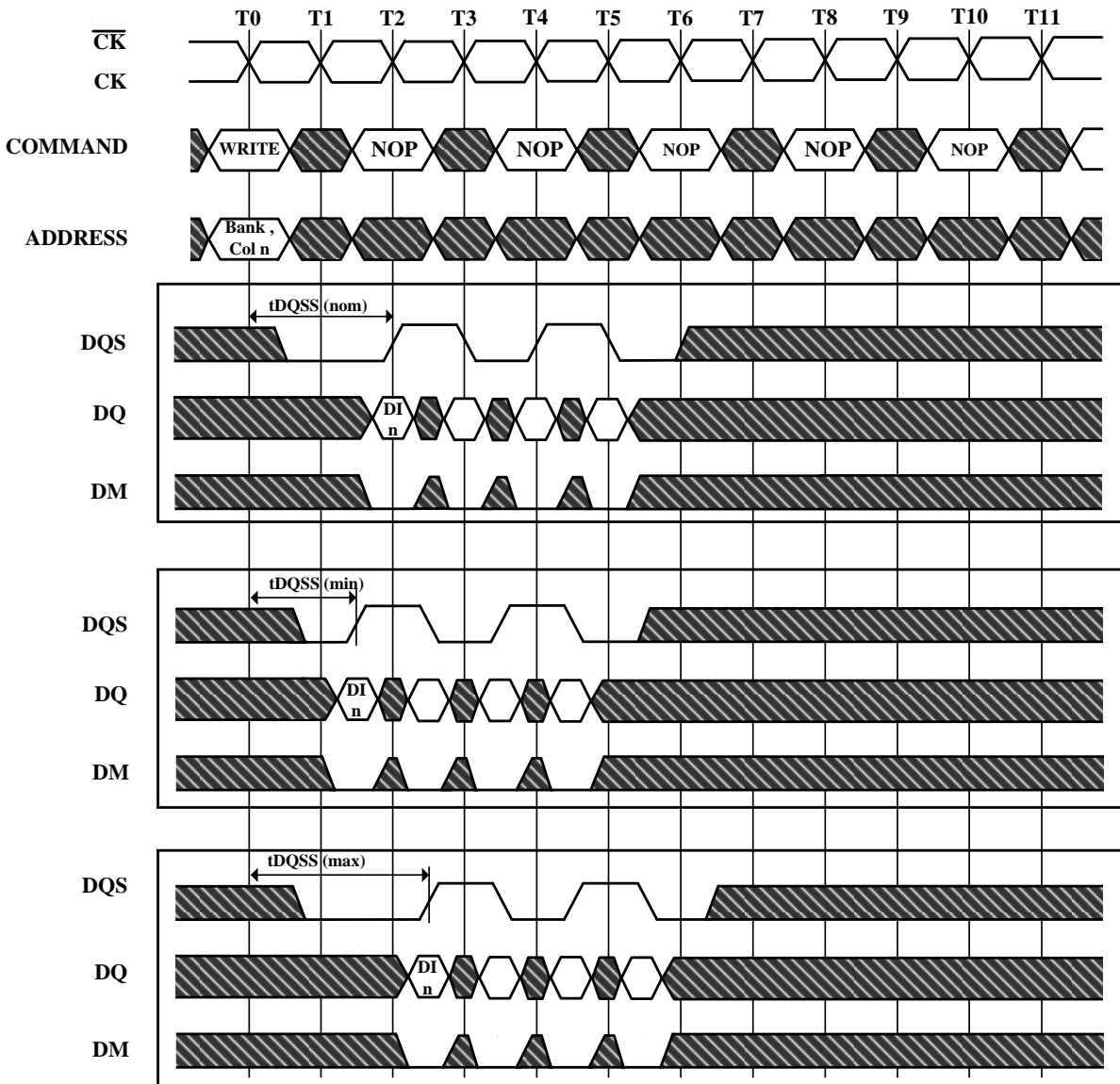
3 subsequent elements of Data In are applied in the programmed order following DI n

A non-interrupted burst of 4 is shown

A8 is LOW with the WRITE command (AUTO PRECHARGE disabled)

 **Don't Care**

Figure 17. Write Burst Nom, Min, and Max tDQSS



DI_n = Data In for column n

3 subsequent elements of Data are applied in the programmed order following DI_n

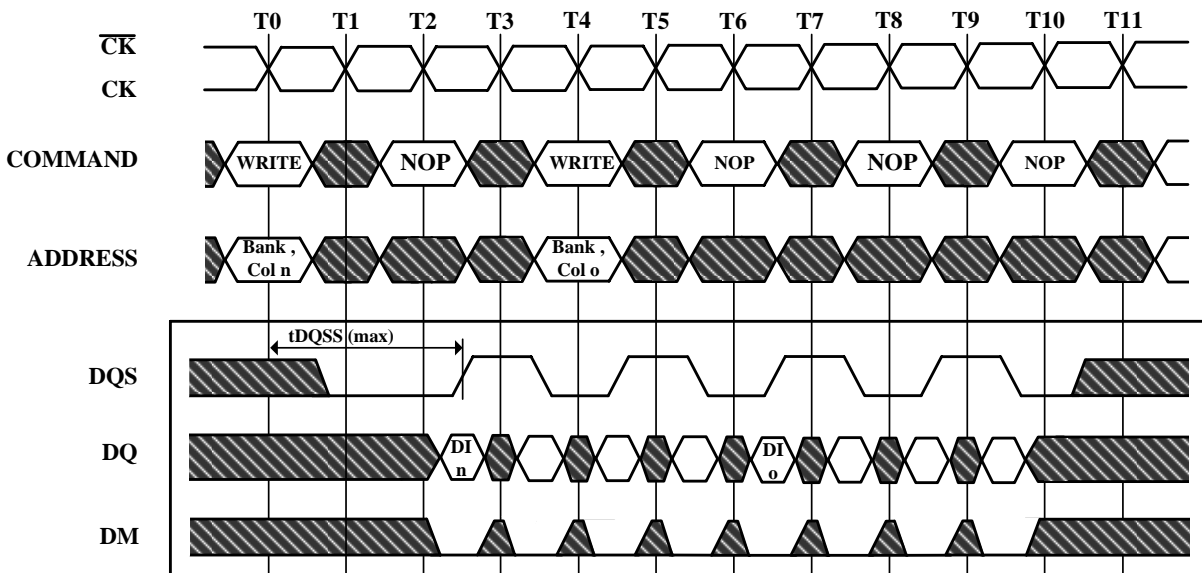
A non-interrupted burst of 4 is shown

A8 is LOW with the WRITE command (AUTO PRECHARGE disabled)

DM=DM0 ~ DM3

 Don't Care

Figure 18. Write to Write Max tDQSS



DI n , etc. = Data In for column n,etc.

3 subsequent elements of Data In are applied in the programmed order following DI n

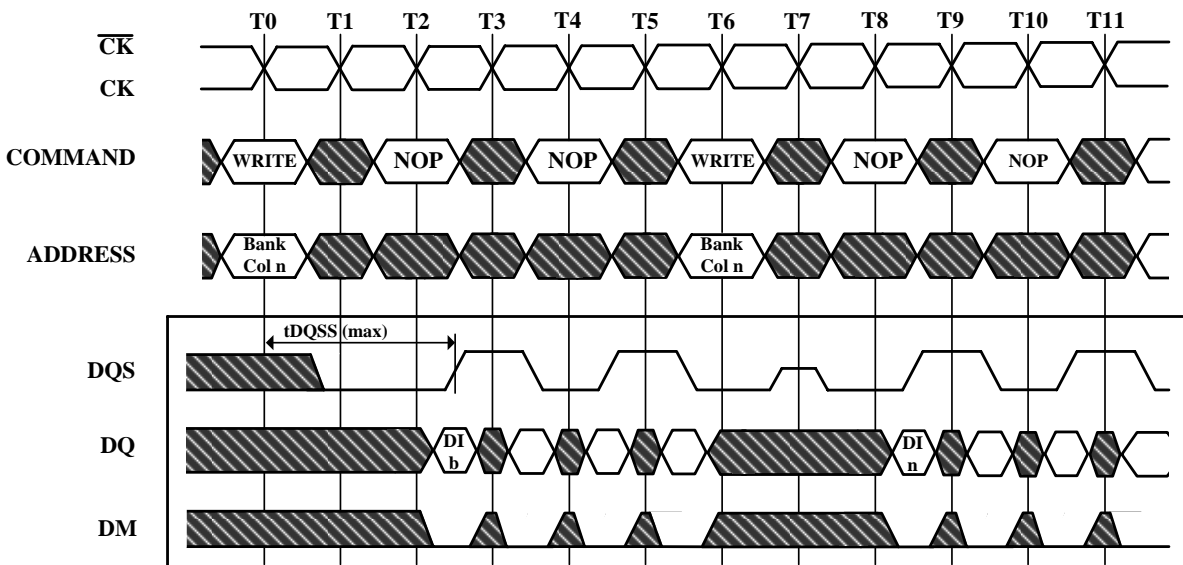
3 subsequent elements of Data In are applied in the programmed order following DI o

Non-interrupted bursts of 4 are shown

DM= DM0 ~ DM3

 Don't Care

Figure 19. Write to Write Max tDQSS, Non Consecutive



DI n, etc. = Data In for column n, etc.

3 subsequent elements of Data In are applied in the programmed order following DI n

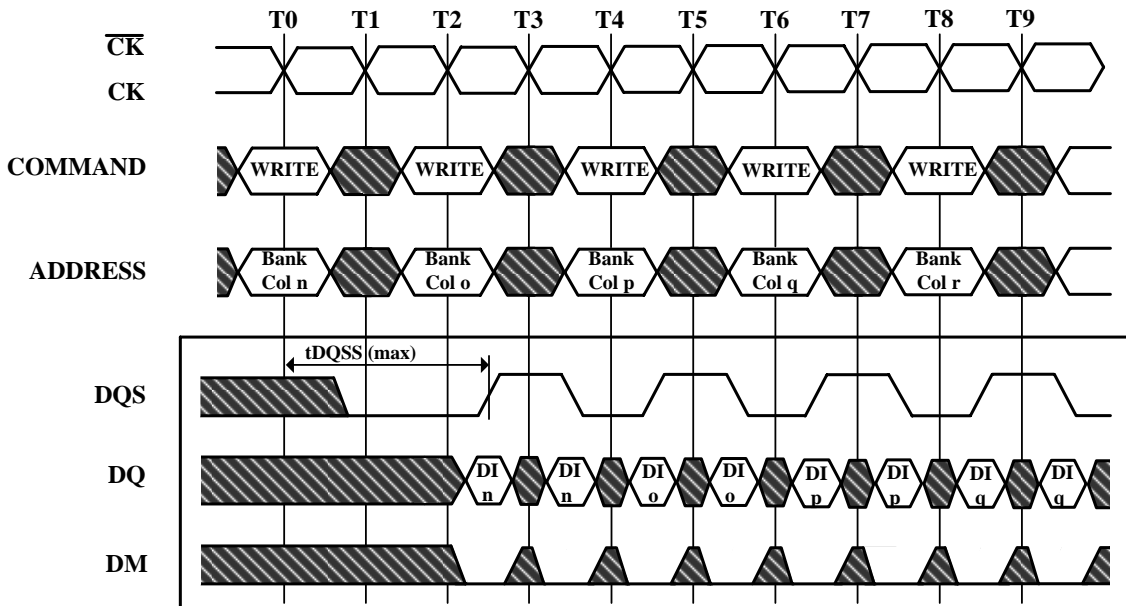
3 subsequent elements of Data In are applied in the programmed order following DI o

Non-interrupted bursts of 4 are shown

DM= DM0 ~ DM3

 Don't Care

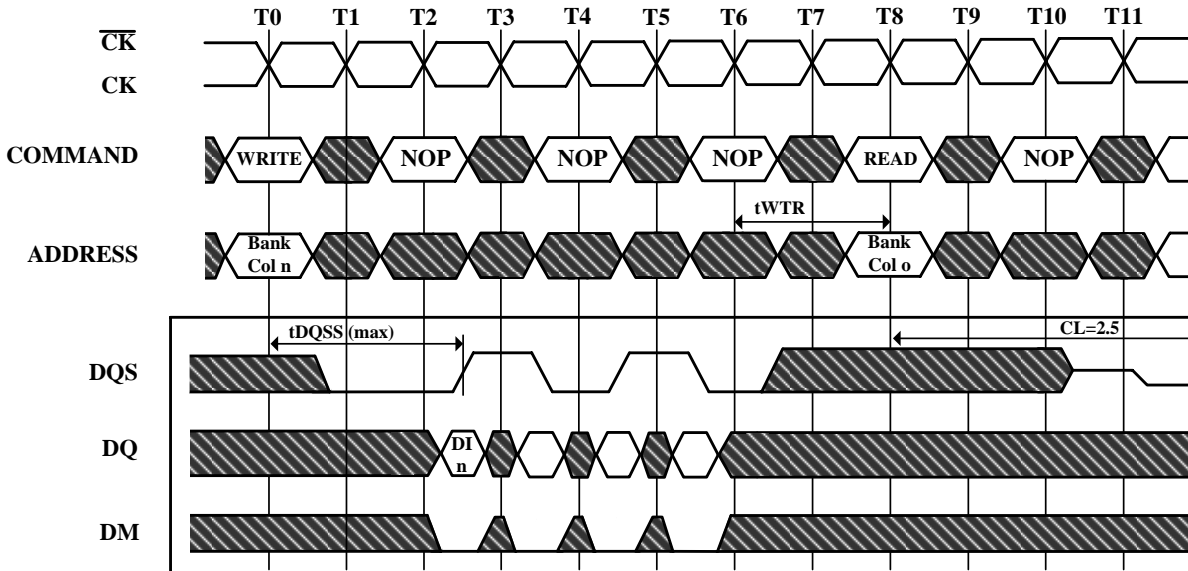
Figure 20. Random Write Cycles Max tDQSS



DI n, etc. = Data In for column n, etc.
 n', etc. = the next Data In following DI n, etc. according to the programmed burst order
 Programmed Burst Length 2, 4, or 8 in cases shown
 If burst of 4 or 8, the burst would be truncated
 Each WRITE command may be to any bank and may be to the same or different devices
 DM= DM0 ~ DM3

 Don't Care

Figure 21. Write to Read Max tDQSS Non Interrupting



DI n, etc. = Data In for column n, etc.

3 subsequent elements of Data In are applied in the programmed order following DI n

A non-interrupted burst of 4 is shown

tWTR is referenced from the first positive CK edge after the last Data In Pair

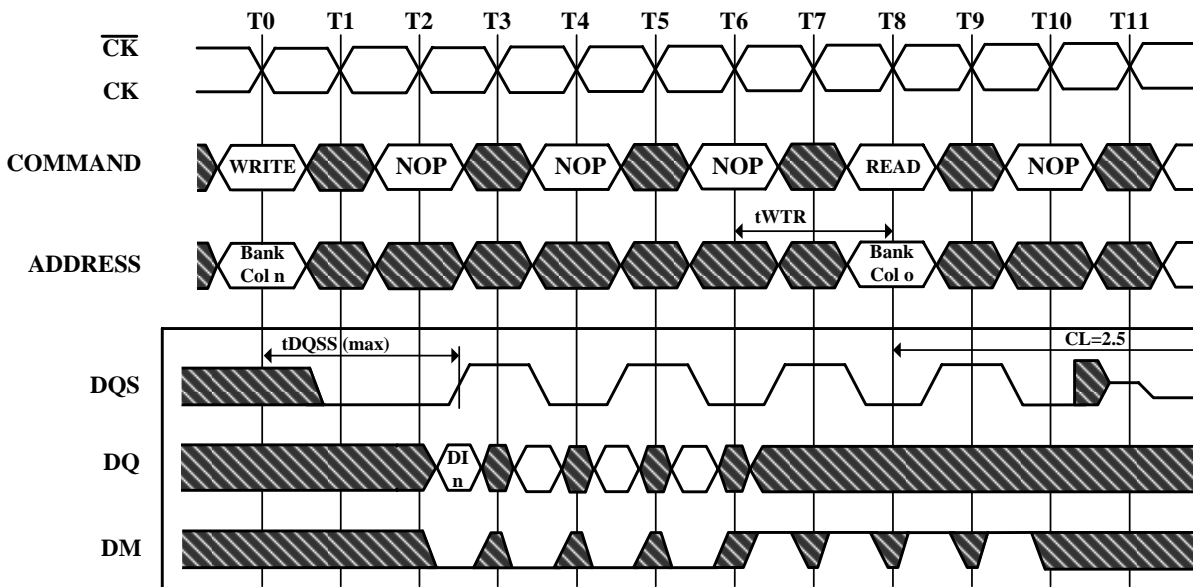
A8 is LOW with the WRITE command (AUTO PRECHARGE is disabled)

The READ and WRITE commands are to the same devices but not necessarily to the same bank

DM= DM0 ~ DM3

 Don't Care

Figure 22. Write to Read Max tDQSS Interrupting



DI n, etc. = Data In for column n, etc.

3 subsequent elements of Data In are applied in the programmed order following DI n

An interrupted burst of 8 is shown, 4 data elements are written

tWTR is referenced from the first positive CK edge after the last Data In Pair

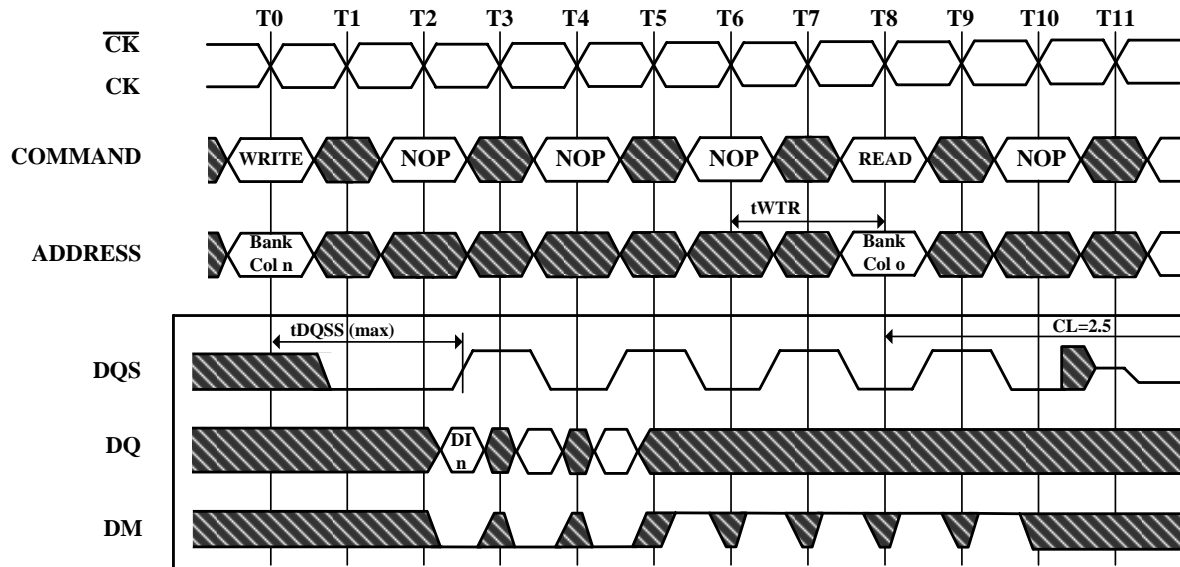
A8 is LOW with the WRITE command (AUTO PRECHARGE is disabled)

The READ and WRITE commands are to the same devices but not necessarily to the same bank

DM= DM0 ~ DM3

 Don't Care

Figure 23. Write to Read Max tDQSS, ODD Number of Data, Interrupting



DI n = Data In for column n

2 subsequent elements of Data In are applied in the programmed order following DI n

An interrupted burst of 8 is shown, 3 data elements are written

tWTR is referenced from the first positive CK edge after the last Data In Pair (not the last desired Data In element)

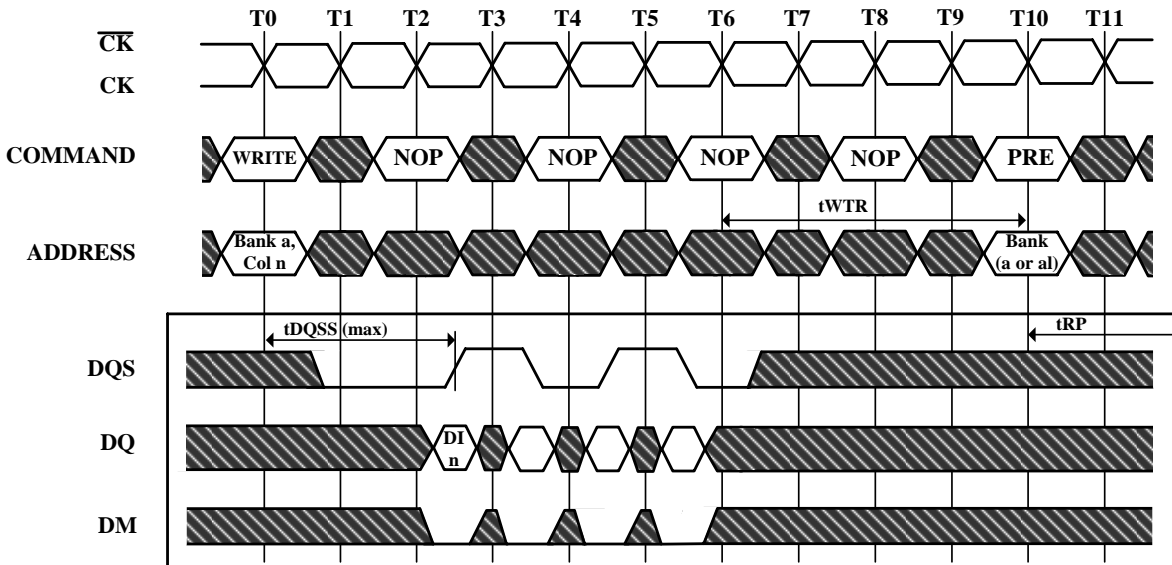
A8 is LOW with the WRITE command (AUTO PRECHARGE is disabled)

The READ and WRITE commands are to the same devices but not necessarily to the same bank

DM= DM0~ DM3

 Don't Care

Figure 24. Write to Precharge Max tDQSS, NON- Interrupting



DI n = Data In for column n

3 subsequent elements of Data In are applied in the programmed order following DI n

A non-interrupted burst of 4 is shown

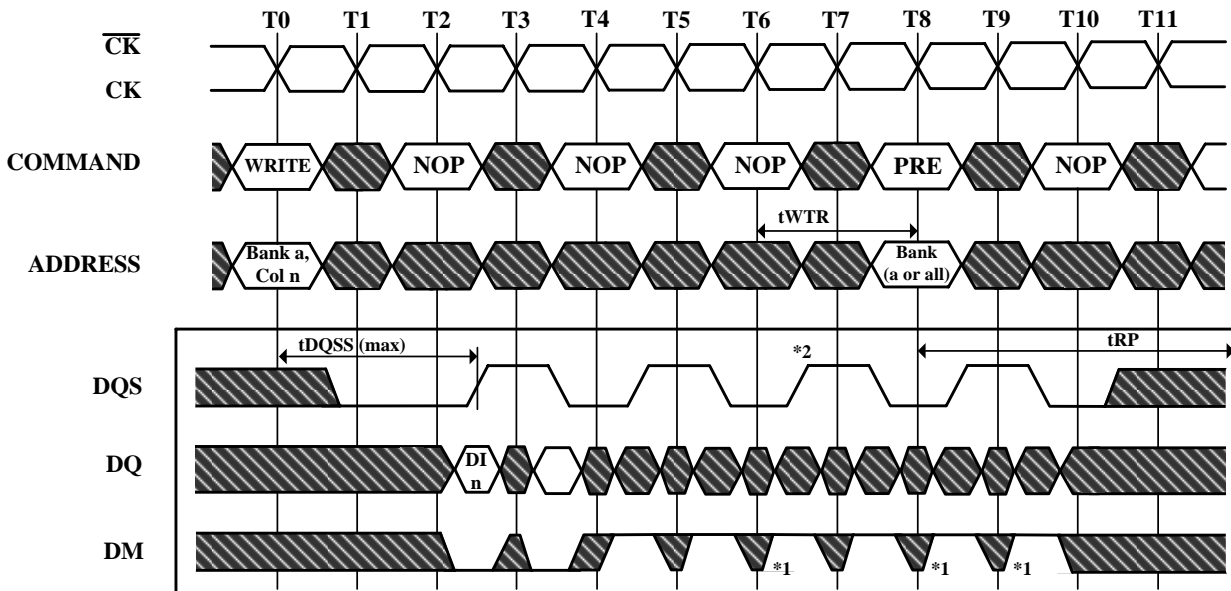
tWTR is referenced from the first positive CK edge after the last Data In Pair

A8 is LOW with the WRITE command (AUTO PRECHARGE is disabled)

DM= DM0 ~ DM3

 Don't Care

Figure 25. Write to Precharge Max tDQSS, Interrupting



DI n = Data In for column n

An interrupted burst of 4 or 8 is shown, 2 data elements are written

tWR is referenced from the first positive CK edge after the last Data In Pair

A8 is LOW with the WRITE command (AUTO PRECHARGE is disabled)

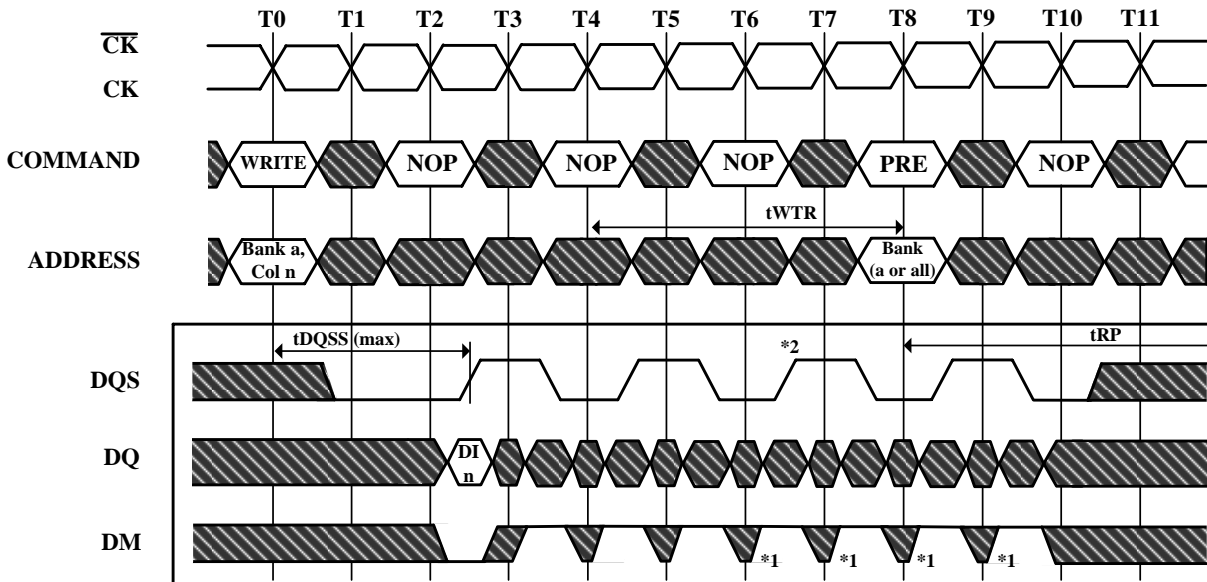
*1 = can be don't care for programmed burst length of 4

*2 = for programmed burst length of 4, DQS becomes don't care at this point

DM= DM 0~ DM3

 Don't Care

Figure 26. Write to Precharge Max tDQSS ODD Number of Data Interrupting



DI n = Data In for column n

An interrupted burst of 4 or 8 is shown, 1 data element is written

tWR is referenced from the first positive CK edge after the last Data In Pair

A8 is LOW with the WRITE command (AUTO PRECHARGE is disabled)

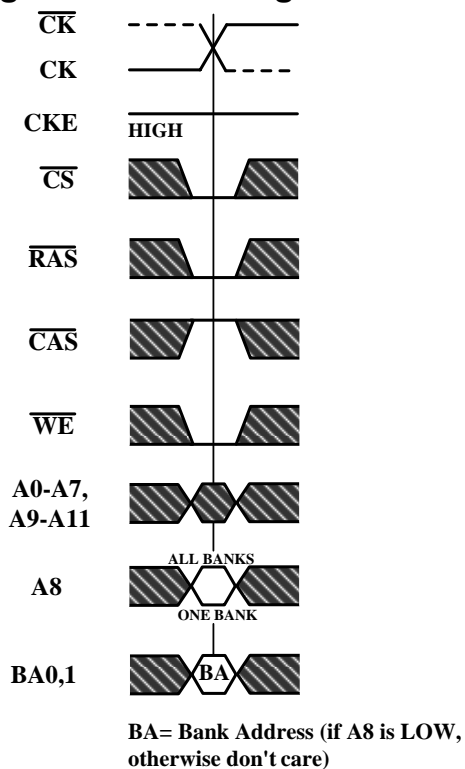
*1 = can be don't care for programmed burst length of 4

*2 = for programmed burst length of 4, DQS becomes don't care at this point

DM= DM0 ~ DM3

 Don't Care

Figure 27. Precharge Command



 Don't Care

Figure 28. Power-Down

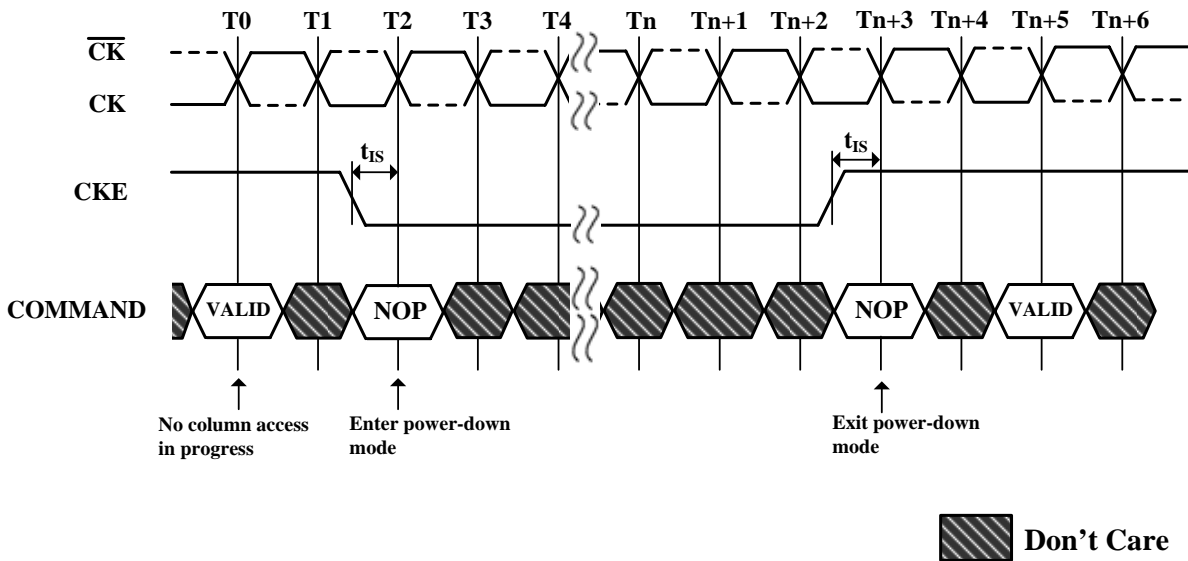


Figure 29. Clock Frequency Change in Precharge

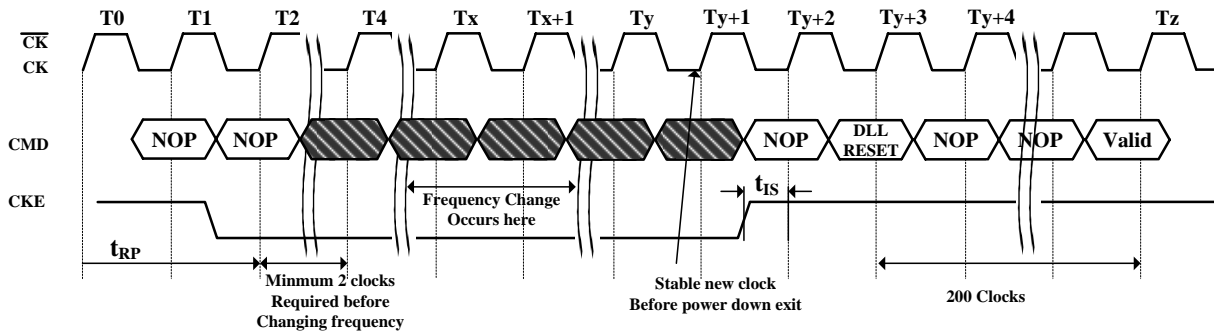
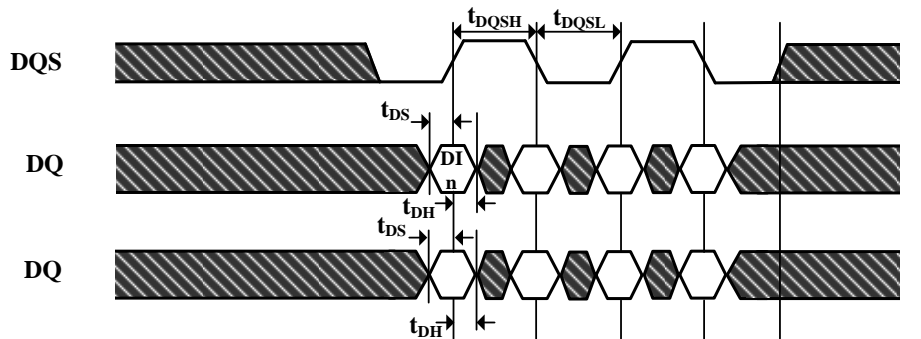


Figure 30. Data input (Write) Timing



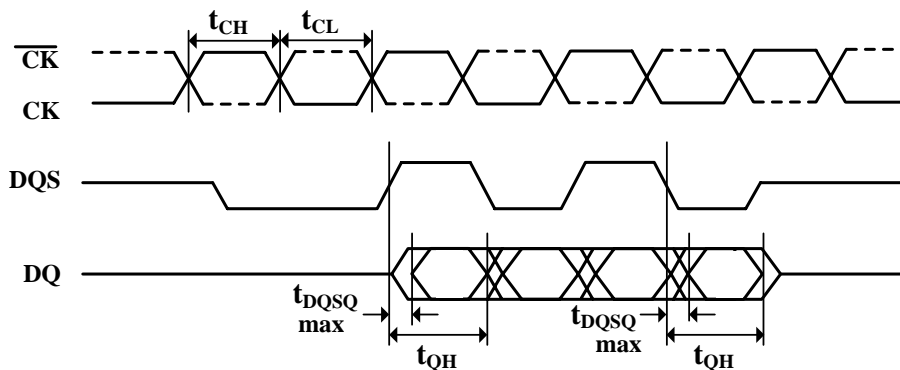
DI n = Data In for column n

Burst Length = 4 in the case shown

3 subsequent elements of Data In are applied in the programmed order following DI n

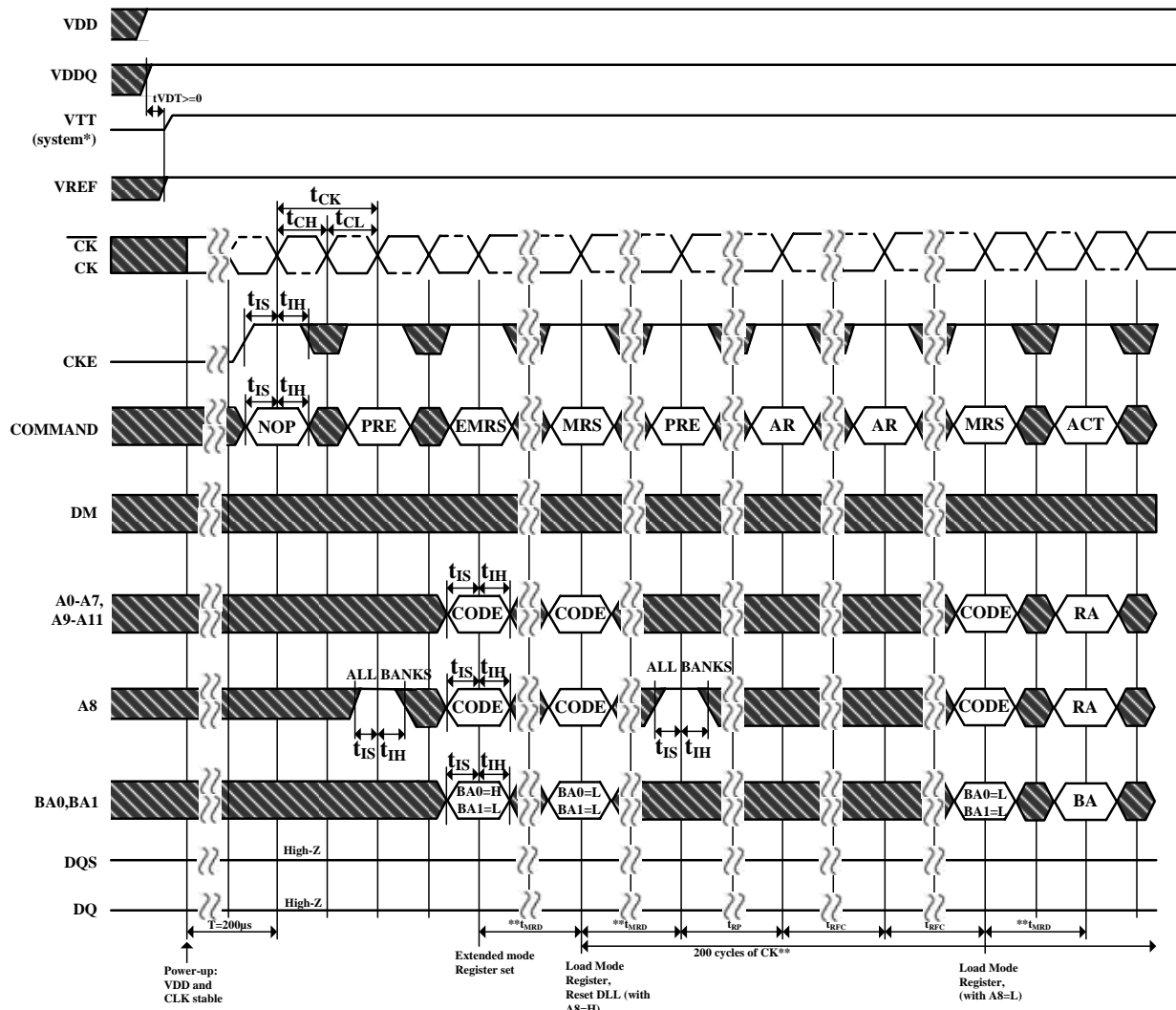
 Don't Care

Figure 31. Data Output (Read) Timing



Burst Length = 4 in the case shown

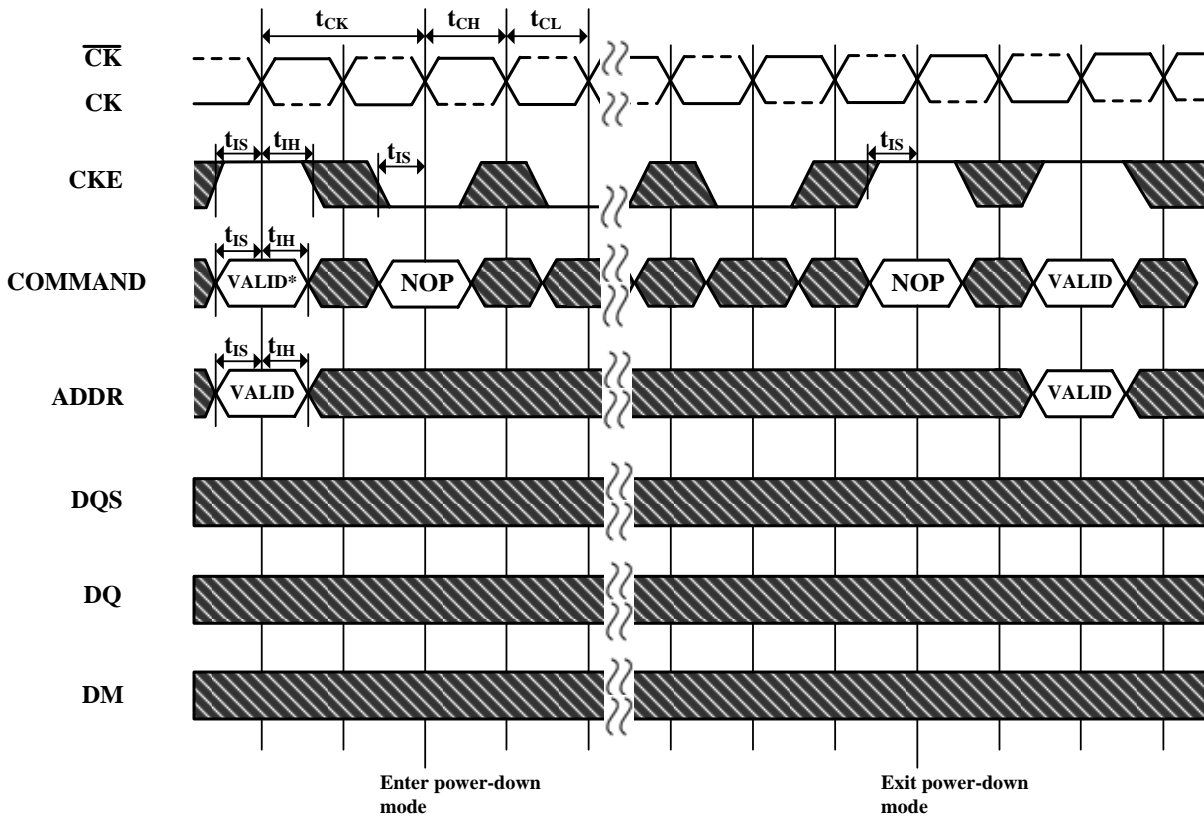
Figure 32. Initialize and Mode Register Sets



*=VTT is not applied directly to the device, however tVTD must be greater than or equal to zero to avoid device latch-up
 =tMRD is required before any command can be applied, and 200 cycles of CK are required before any executable command can be applied
 The two Auto Refresh commands may be moved to follow the first MRS but precede the second PRECHARGE ALL command

 Don't Care

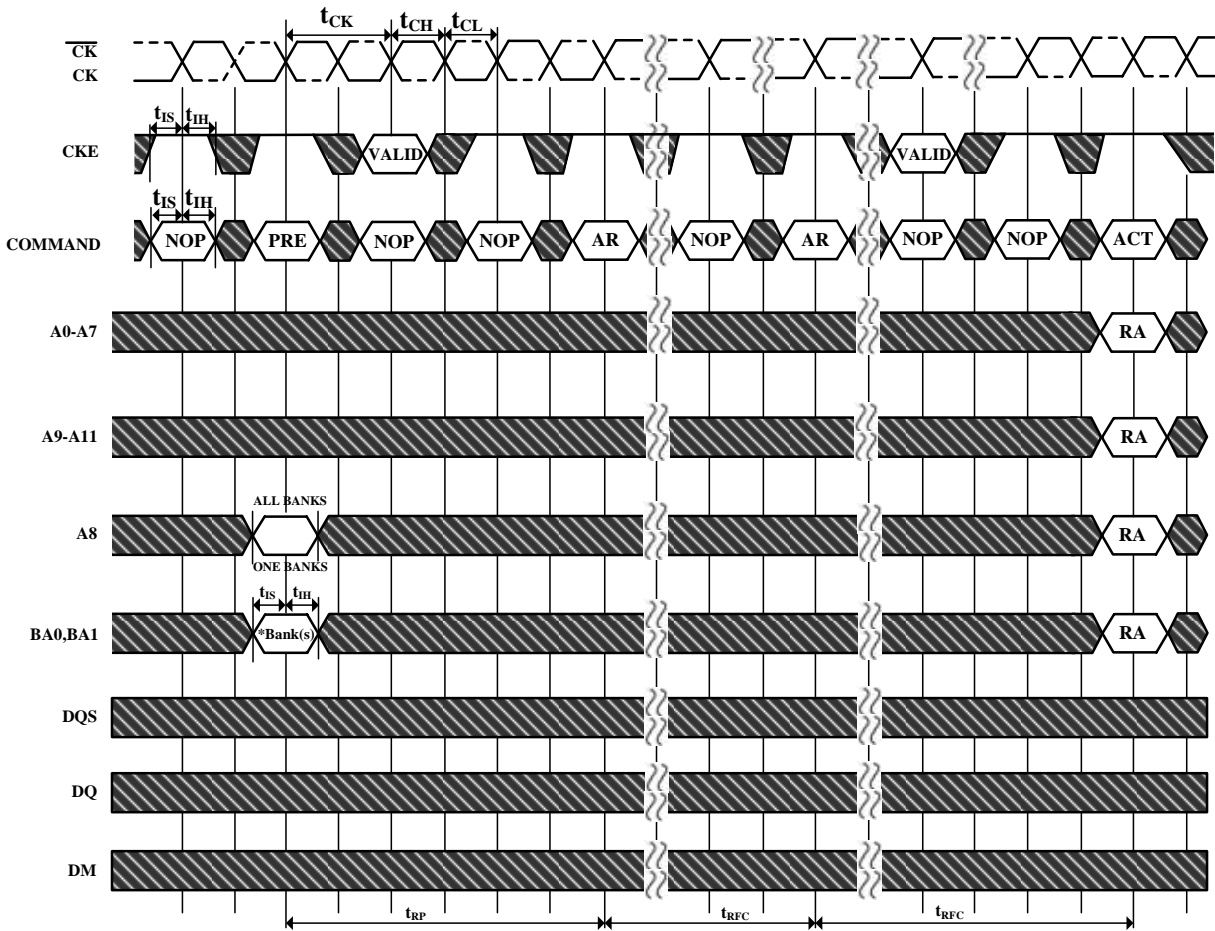
Figure 33. Power Down Mode



No column accesses are allowed to be in progress at the time Power-Down is entered
 *=If this command is a PRECHARGE ALL (or if the device is already in the idle state) then the Power-Down mode shown is Precharge Power Down. If this command is an ACTIVE (or if at least one row is already active) then the Power-Down mode shown is active Power Down.

 Don't Care

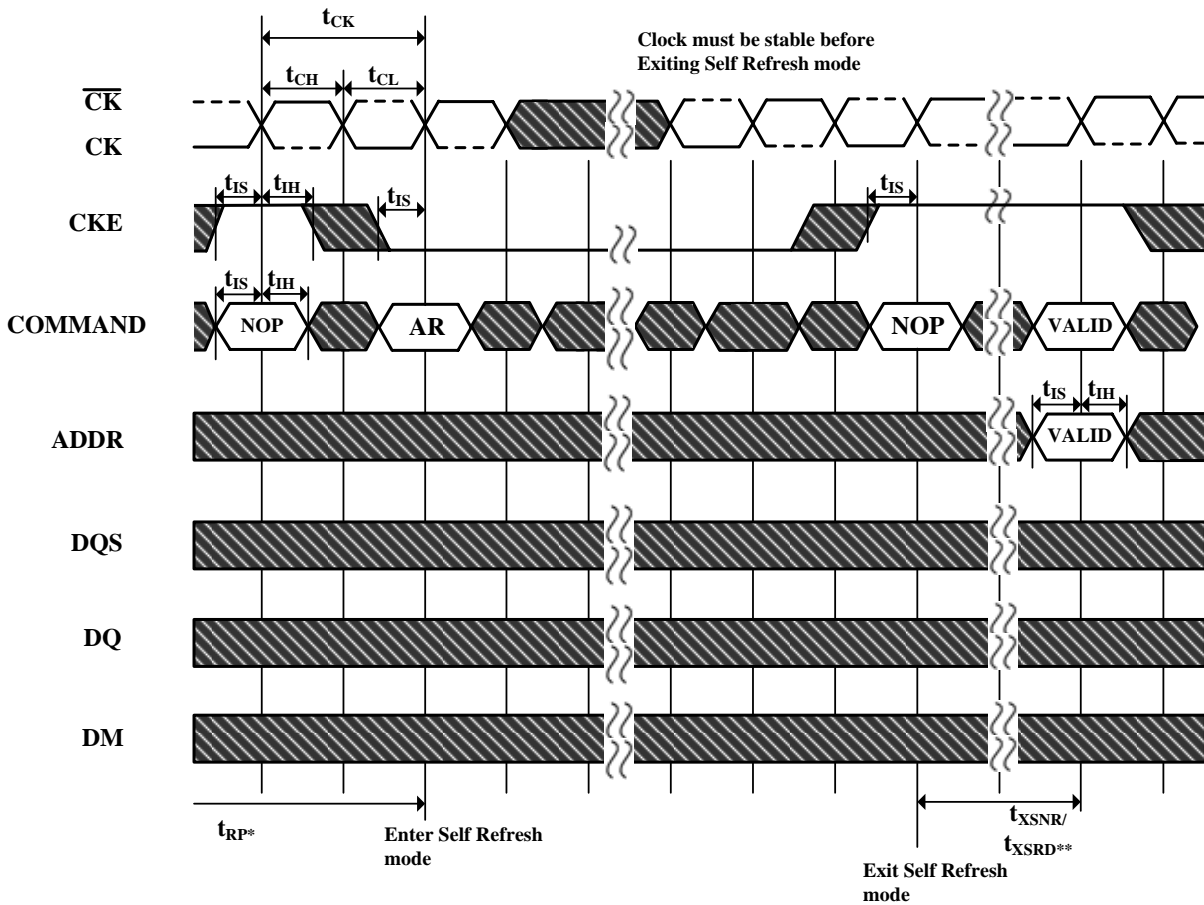
Figure 34. Auto Refresh Mode



* = Don't Care, if A10 is HIGH at this point; A10 must be HIGH if more than one bank is active (i.e., must precharge all active banks)
 PRE = PRECHARGE, ACT = ACTIVE, RA = Row Address, BA = Bank Address, AR = AUTOREFRESH
 NOP commands are shown for ease of illustration; other valid commands may be possible after t_{RFC}
 DM, DQ and DQS signals are all Don't Care /High-Z for operations shown

 Don't Care

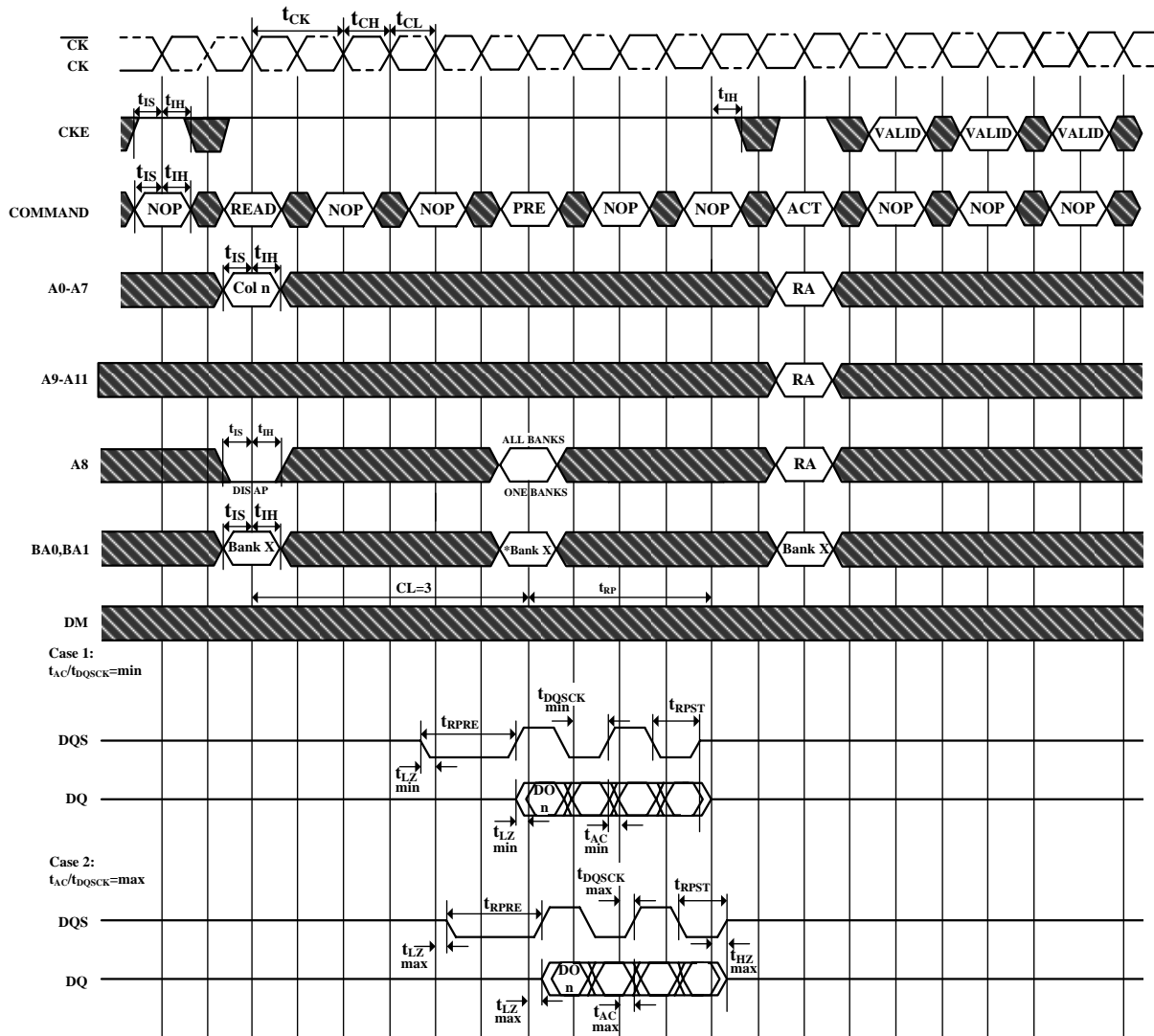
Figure 35. Self Refresh Mode



* = Device must be in the All banks idle state prior to entering Self Refresh mode
 ** = tXSNR is required before any non-READ command can be applied, and tXSRD (200 cycles of CK) is required before a READ command can be applied.

 Don't Care

Figure 36. Read without Auto Precharge



DO n = Data Out from column n
 Burst Length = 4 in the case shown
 3 subsequent elements of Data Out are provided in the programmed order following DO n
 DIS AP = Disable Autoprecharge

* = Don't Care, if A10 is HIGH at this point

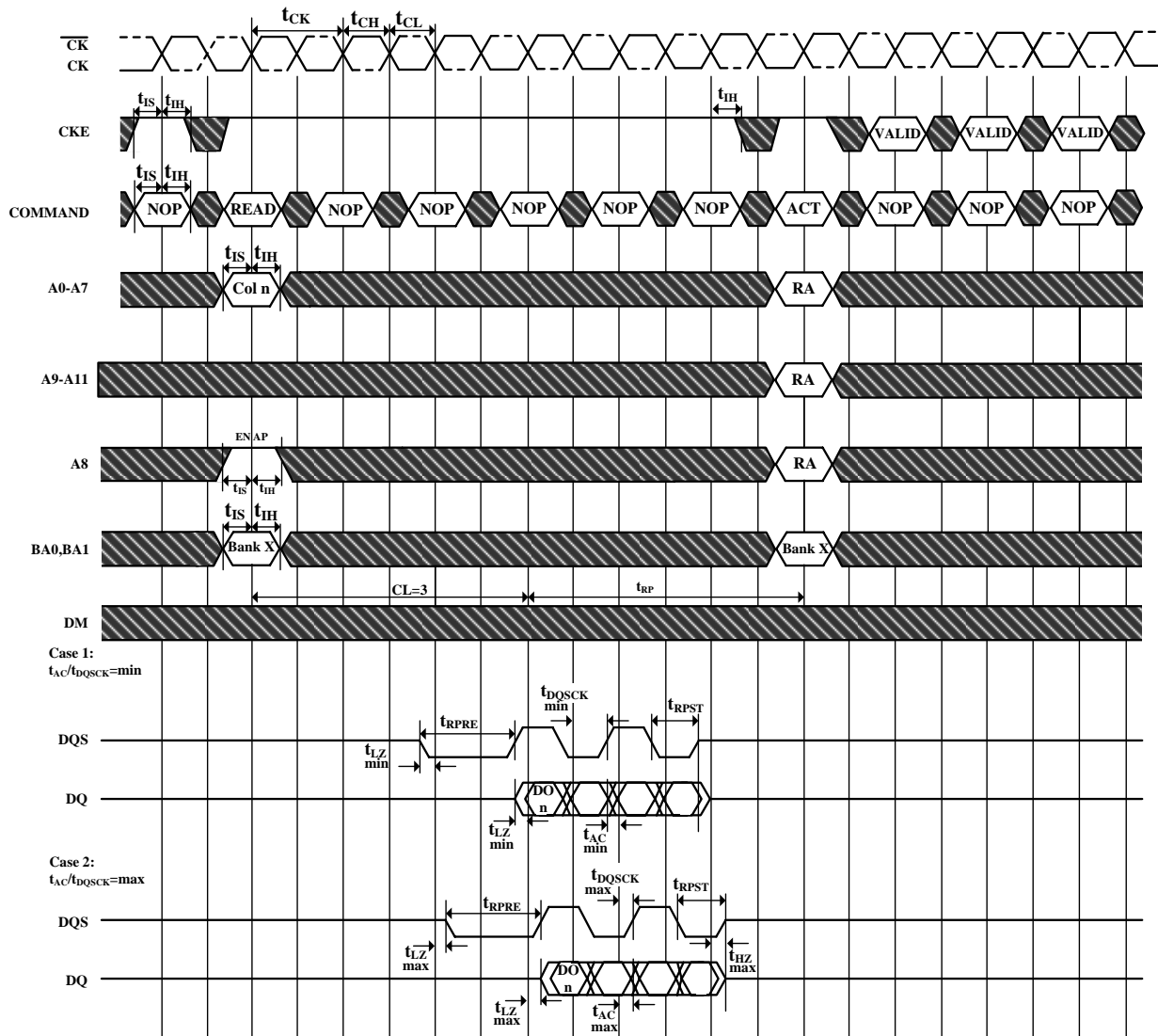
PRE = PRECHARGE, ACT = ACTIVE, RA = Row Address, BA = Bank Address, AR = AUTOREFRESH

NOP commands are shown for ease of illustration; other commands may be valid at these times

Precharge may not be issued before tRAS ns after the ACTIVE command for applicable banks

 Don't Care

Figure 37. Read with Auto Precharge



DO n = Data Out from column n

Burst Length = 4 in the case shown

3 subsequent elements of Data Out are provided in the programmed order following DO n

EN AP = Enable Autoprecharge

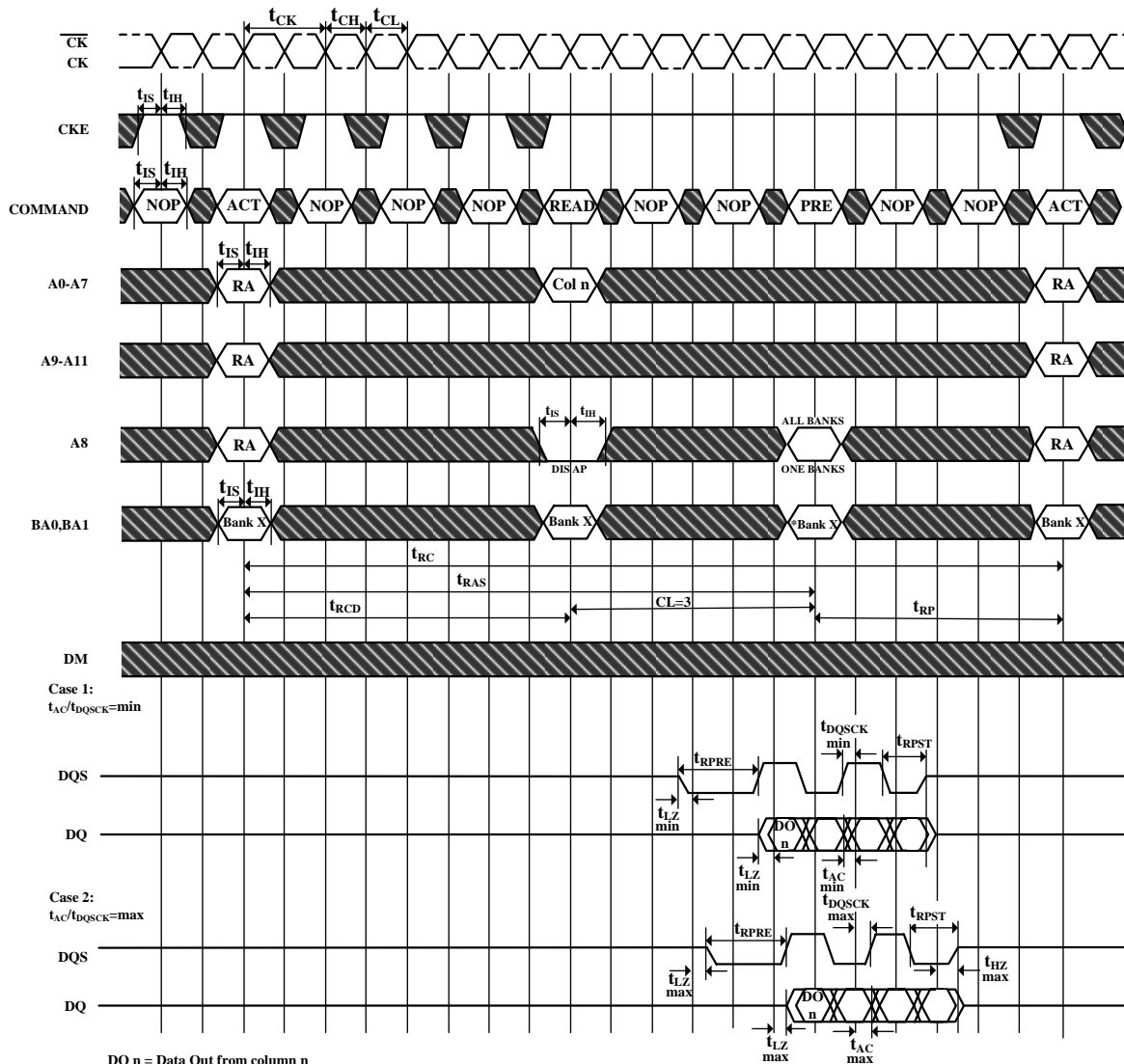
ACT = ACTIVE, RA = Row Address

NOP commands are shown for ease of illustration; other commands may be valid at these times

The READ command may not be issued until tRAP has been satisfied. If Fast Autoprecharge is supported, tRAP = tRCD, else the READ may not be issued prior to tRASmin (BL*tCK/2)

 Don't Care

Figure 38. Bank Read Access



DO n = Data Out from column n
 Burst Length = 4 in the case shown
 3 subsequent elements of Data Out are provided in the programmed order following DO n

DIS AP = Disable Autoprecharge

* = Don't Care, if A10 is HIGH at this point

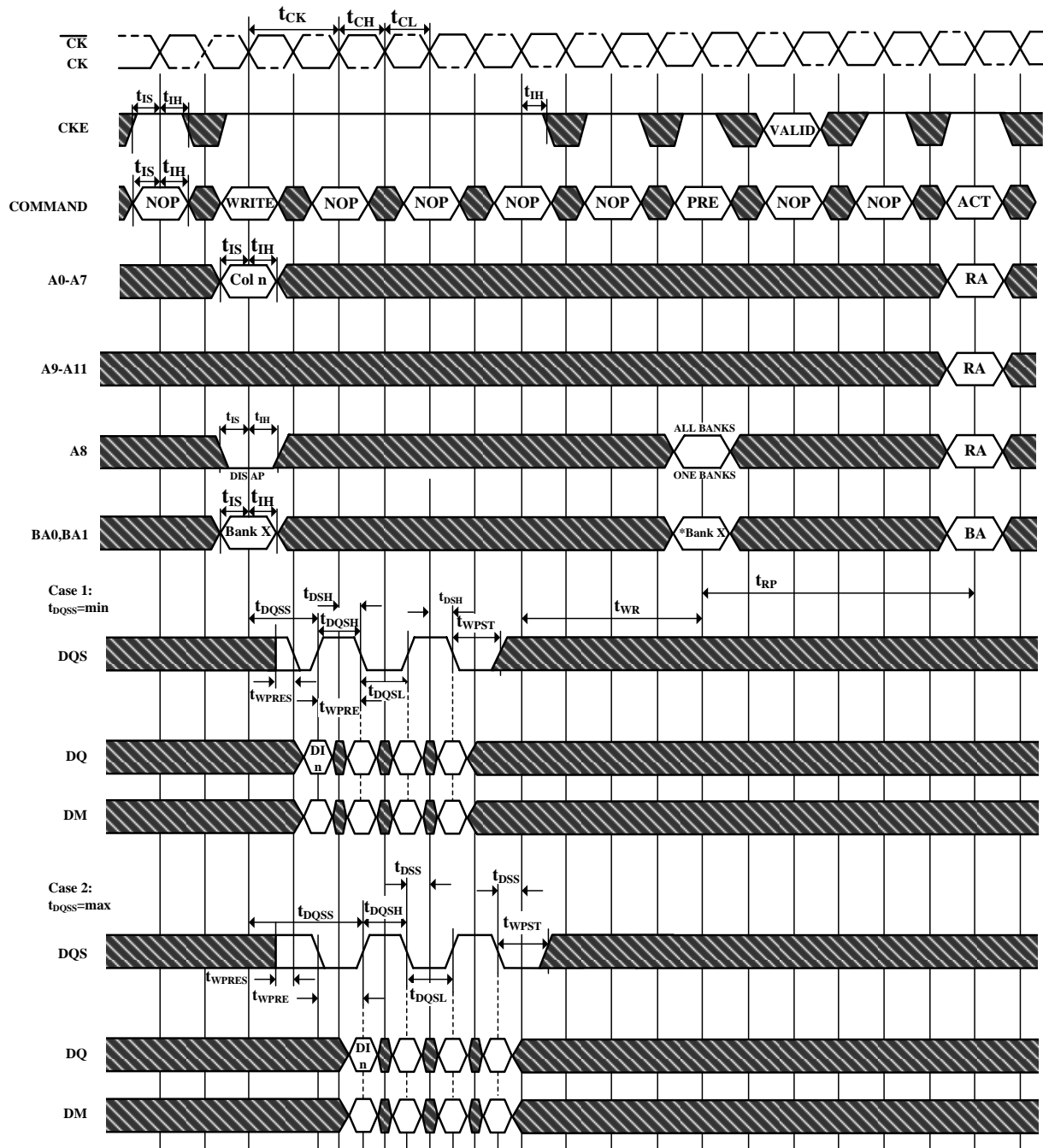
PRE = PRECHARGE, ACT = ACTIVE, RA = Row Address, BA = Bank Address

NOP commands are shown for ease of illustration; other commands may be valid at these times

Note that $t_{RCD} > t_{RCD\ MIN}$ so that the same timing applies if Autoprecharge is enabled (in which case t_{RAS} would be limiting)

 Don't Care

Figure 39. Write without Auto Precharge



DI n = Data In from column n

Burst Length = 4 in the case shown

3 subsequent elements of Data In are provided in the programmed order following DI n

DIS AP = Disable Autoprecharge

* = Don't Care, if A10 is HIGH at this point

PRE = PRECHARGE, ACT = ACTIVE, RA = Row Address, BA = Bank Address, AR = AUTOREFRESH

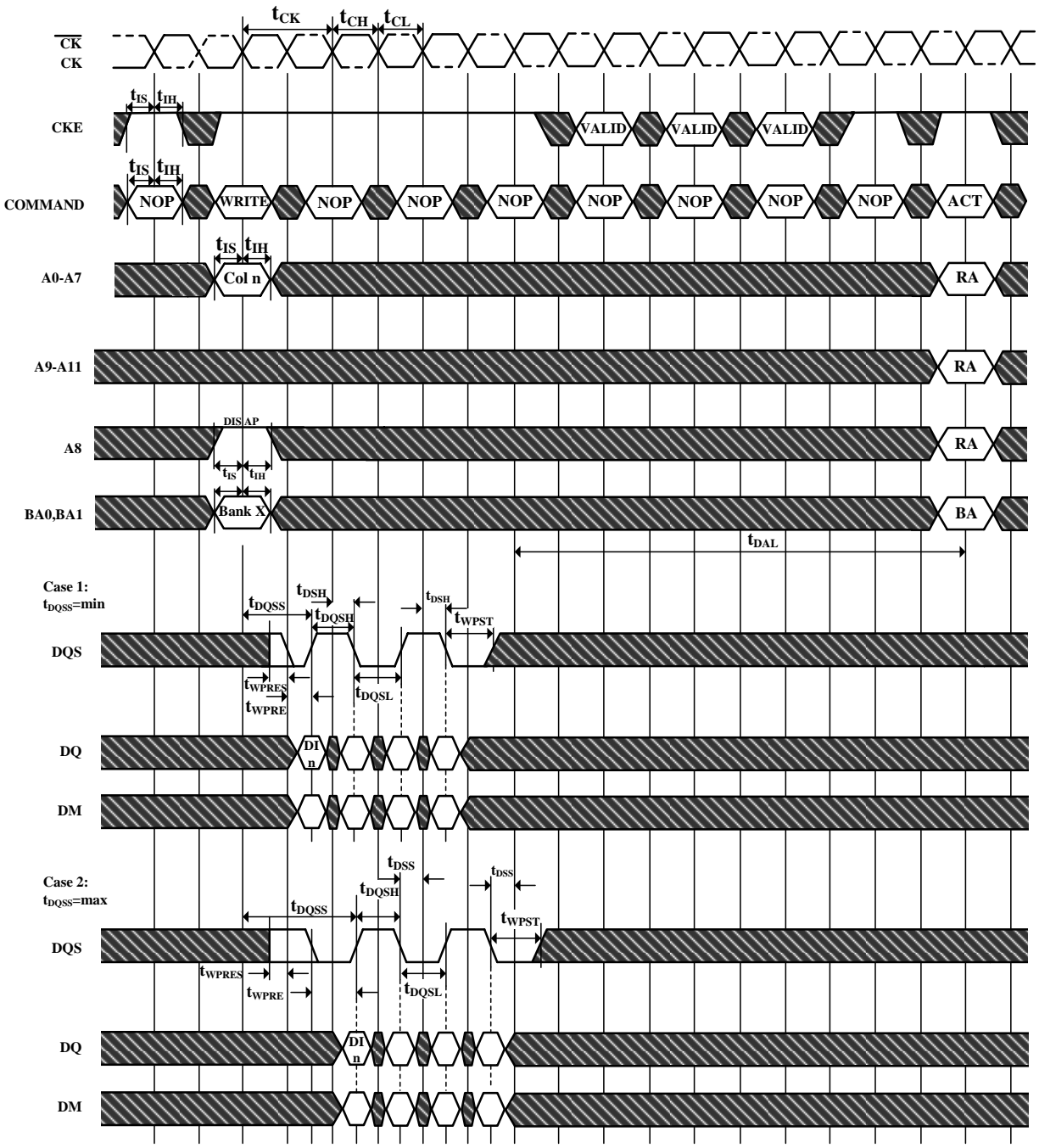
NOP commands are shown for ease of illustration; other commands may be valid at these times

Although t_{DQSS} is drawn only for the first DQS rising edge, each rising edge of DQS must fall within the $\pm 25\%$ window of the corresponding positive clock edge

Precharge may not be issued before t_{RAS} ns after the ACTIVE command for applicable banks

 Don't Care

Figure 40. Write with Auto Precharge



DI n = Data In from column n

Burst Length = 4 in the case shown

3 subsequent elements of Data Out are provided in the programmed order following DI n

EN AP = Enable Autoprecharge

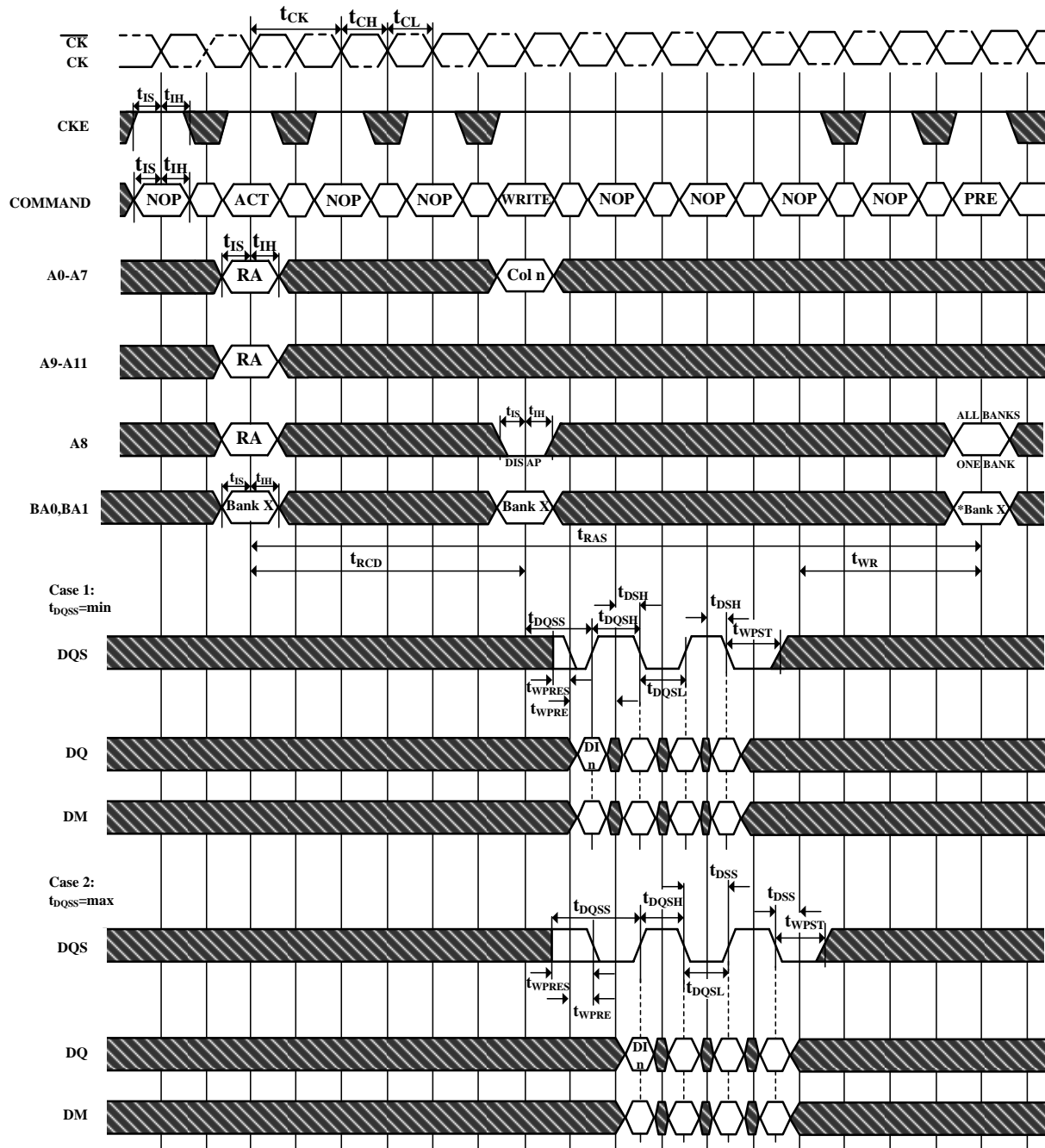
ACT = ACTIVE, RA = Row Address, BA = Bank Address

NOP commands are shown for ease of illustration; other commands may be valid at these times

Although tDQSS is drawn only for the first DQS rising edge, each rising edge of DQS must fall within the ± 25% window of the corresponding positive clock edge

 Don't Care

Figure 41. Bank Write Access



DI n = Data In from column n

Burst Length = 4 in the case shown

3 subsequent elements of Data Out are provided in the programmed order following DI n

DIS AP = Disable Autoprecharge

*= Don't Care, if A10 is HIGH at this point

PRE = PRECHARGE, ACT = ACTIVE, RA = Row Address, BA = Bank Address

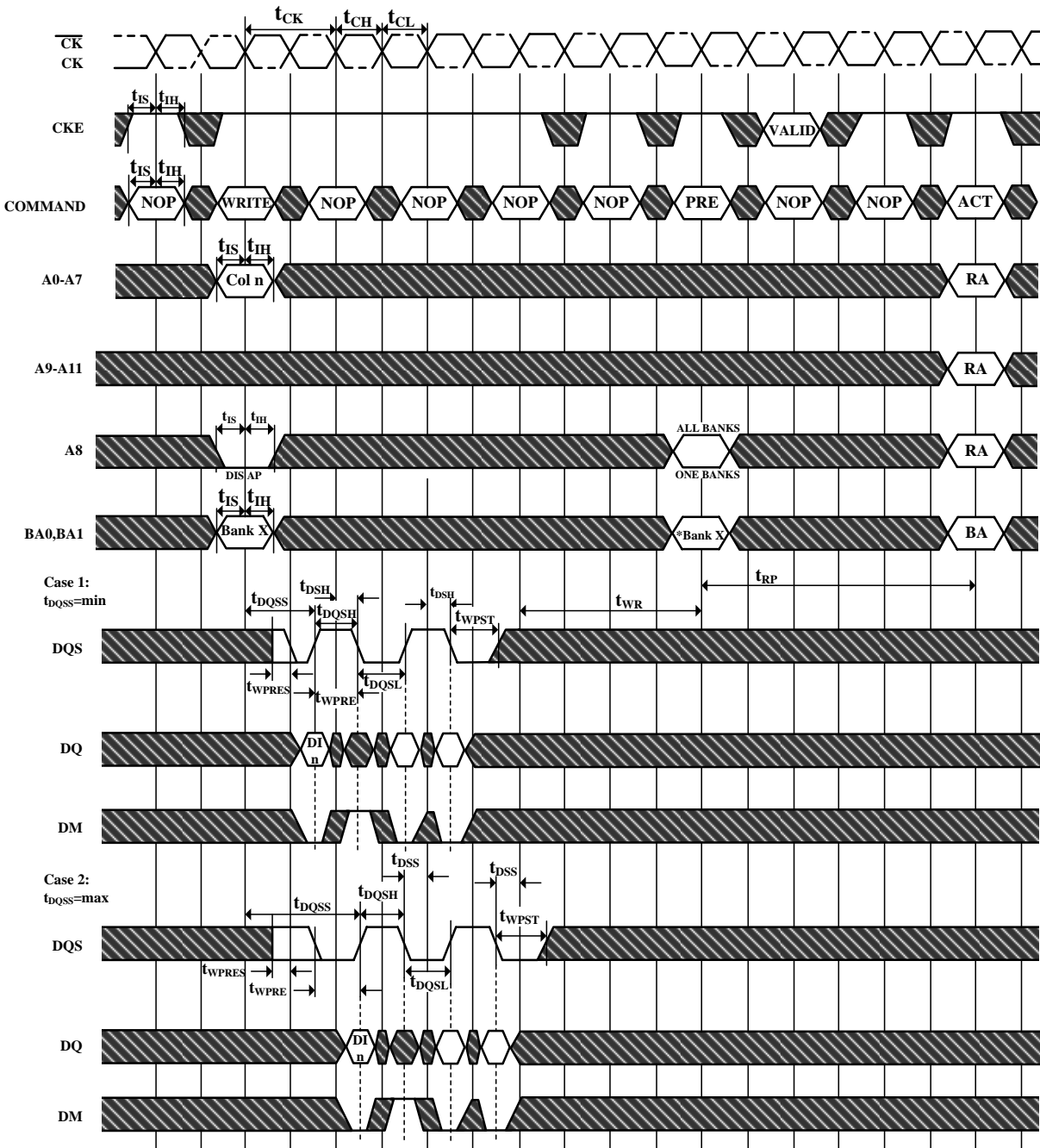
NOP commands are shown for ease of illustration; other commands may be valid at these times

Although tDQSS is drawn only for the first DQS rising edge, each rising edge of DQS must fall within the $\pm 25\%$ window of the corresponding positive clock edge

Precharge may not be issued before tRAS ns after the ACTIVE command for applicable banks

 Don't Care

Figure 42. Write DM Operation



DI n = Data In from column n

Burst Length = 4 in the case shown

3 subsequent elements of Data In are provided in the programmed order following DI n

DIS AP = Disable Autoprecharge

*= Don't Care, if A10 is HIGH at this point

PRE = PRECHARGE, ACT = ACTIVE, RA = Row Address, BA = Bank Address

NOP commands are shown for ease of illustration; other commands may be valid at these times

Although t_{DQSS} is drawn only for the first DQS rising edge, each rising edge of DQS must fall within the $\pm 25\%$ window of the corresponding positive clock edge

Precharge may not be issued before t_{RAS} ns after the ACTIVE command for applicable banks



Figure 43. 144 ball TFBGA Package Outline Drawing Information
Units: mm

